

bq40z60 Programmable Battery Management Unit

1 Features

- Fully Integrated 2-Series to 4-Series Cell Li-Ion or Li-Polymer Battery Management Unit
- Input Voltage Range on Pack+: 2.5 V to 25 V
- Battery Charger Efficiency > 92%
- Battery Charger Operation Range: 4 V to 25 V
- Battery Charger, 1-MHz Synchronous Buck Controller for External NFETs
 - Soft Start to Limit In-Rush Current
 - Current Limit Protection for External Switches
 - Programmable Charging
 - Supports JEITA/Enhanced Charging Modes
- Fuel Gauging
 - High Resolution 16-Bit Integrator for Coulomb Counter
 - ADC, 16-Bit for Precision V, I, and T Measurements with 16-Channel Multiplexer
 - Support for Simultaneous CC and ADC Sampling (Power Conversion)
 - Supports Two-Wire SMBus v2.0 Interface with Accelerated 400-kHz Programming Option
 - SHA-1 Hash Message Authentication Code (HMAC) Responder for Increased Battery Pack Security
 - Split Key (2 × 64) Stored in Secure Memory
 - Supports Field Updates
- AFE Protection
 - Programmable Current Protection
 - Overcurrent in Discharge
 - Short-Circuit Current in Charge
 - Short-Circuit Current in Discharge
- N-FET High-Side Protection FET Drive
- Support for Four LEDs
- Thermistor inputs for NTC
- Compact 32-Pin QFN Package (RHB)

2 Applications

- Notebooks, Ultrabooks, Netbooks, Tablets, UMPCs
- Medical and Test Equipment
- Portable Instrumentation

3 Description

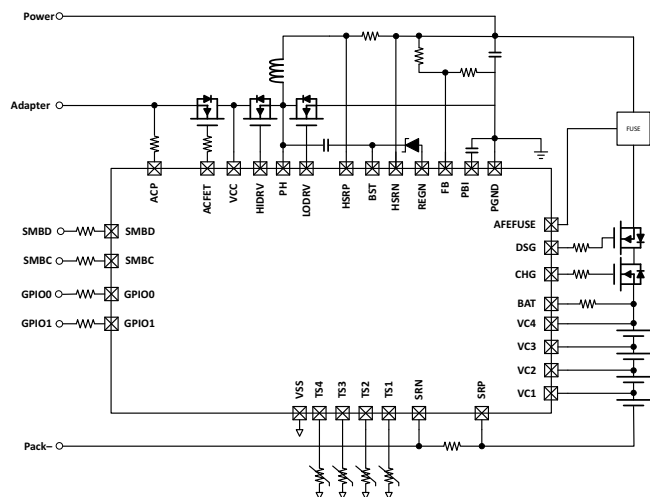
The Texas Instruments bq40z60 device is a Programmable Battery Management Unit that integrates battery charging control output, gas gauging, and protection for completely autonomous operation of 2-series to 4-series cell Li-Ion and Li-Polymer battery packs. The architecture enables internal communication between the fuel gauging processor and battery charger controller to optimize the charging profile based on the external load conditions and power path source management during load transients and adaptor current limitations in the system. The charging current efficiency is scalable for power transfer based on the external components, such as the NFETs, inductor, and sensing resistor.

Device Information⁽¹⁾

| PART NUMBER | PACKAGE | BODY SIZE (NOM) |
|-------------|-----------|-------------------|
| bq40z60 | VQFN (32) | 5.00 mm × 5.00 mm |

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic



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Table of Contents

| | | | |
|---|----------|---|-----------|
| 1 Features | 1 | 7.33 Battery Charger Precharge Current Sense (HSRP, HSRN) | 15 |
| 2 Applications | 1 | 7.34 AC Adapter Fault Detect (HSRN, VCC) | 15 |
| 3 Description | 1 | 7.35 Battery Charger Overcurrent Detection (V) _{HSRP} , (V) _{HSRN} | 15 |
| 4 Revision History | 2 | 7.36 Battery Charger Undercurrent Detection (V) _{HSRP} , (V) _{HSRN} | 15 |
| 5 Description (continued) | 3 | 7.37 System Operation Detection (V) _{HSRN} | 15 |
| 6 Pin Configuration and Functions | 3 | 7.38 Battery Overvoltage Comparator (VFB) | 15 |
| 7 Specifications | 5 | 7.39 Regulator (REGN) | 16 |
| 7.1 Absolute Maximum Ratings | 5 | 7.40 PWM High-Side Driver (HiDRV) | 16 |
| 7.2 ESD Ratings | 5 | 7.41 PWM Low-Side Driver (LoDRV) | 16 |
| 7.3 Recommended Operating Conditions | 5 | 7.42 PWM Information | 16 |
| 7.4 Thermal Information | 6 | 7.43 Charger Power-Up Sequence | 16 |
| 7.5 Supply Voltage | 6 | 7.44 Thermal Shutdown Comparator | 16 |
| 7.6 Supply Current | 7 | 7.45 SMBus High Voltage I/O | 17 |
| 7.7 Power Supply Control | 7 | 7.46 SMBus | 17 |
| 7.8 Low-Voltage General Purpose I/O (TSx) | 7 | 7.47 SMBus XL | 17 |
| 7.9 High-Voltage General Purpose I/O (GPIO0, GPIO1) | 8 | 7.48 Timing Requirements | 18 |
| 7.10 AFE Power-On Reset | 8 | 7.49 Typical Characteristics | 18 |
| 7.11 Internal 1.8-V LDO | 8 | 8 Detailed Description | 19 |
| 7.12 Current Wake Comparator | 9 | 8.1 Overview | 19 |
| 7.13 Coulomb Counter | 9 | 8.2 Functional Block Diagram | 20 |
| 7.14 CC Digital Filter | 9 | 8.3 Feature Description | 21 |
| 7.15 ADC | 9 | 9 Application and Implementation | 29 |
| 7.16 ADC Digital Filter | 10 | 9.1 Application Information | 29 |
| 7.17 ADC Multiplexer | 10 | 9.2 Typical Applications | 30 |
| 7.18 Cell Balancing Support | 10 | 10 Power Supply Recommendations | 34 |
| 7.19 Cell Detach Detection | 10 | 11 Layout | 34 |
| 7.20 Internal Temperature Sensor | 11 | 11.1 Layout Guidelines | 34 |
| 7.21 NTC Thermistor Measurement Support (ADCx) | 11 | 11.2 Layout Example | 36 |
| 7.22 High-Frequency Oscillator | 11 | 12 Device and Documentation Support | 37 |
| 7.23 Low-Frequency Oscillator | 11 | 12.1 Related Documentation | 37 |
| 7.24 Voltage Reference 1 | 11 | 12.2 Community Resources | 37 |
| 7.25 Voltage Reference 2 | 12 | 12.3 Trademarks | 37 |
| 7.26 Instruction Flash | 12 | 12.4 Electrostatic Discharge Caution | 37 |
| 7.27 Data Flash | 12 | 12.5 Glossary | 37 |
| 7.28 Current Protection Thresholds | 12 | 13 Mechanical, Packaging, and Orderable Information | 37 |
| 7.29 N-CH FET Drive (CHG, DSG) | 13 | | |
| 7.30 FUSE Drive (AFE FUSE) | 14 | | |
| 7.31 Battery Charger Voltage Regulation (VFB) | 14 | | |
| 7.32 Battery Charger Current Sense (HSRP, HSRN) | 14 | | |

4 Revision History

| Changes from Revision C (July 2015) to Revision D | Page |
|---|-----------|
| • Changed Simplified Schematic | 1 |
| • Changed Pin Configuration and Functions | 3 |
| • Changed Absolute Maximum Ratings | 5 |
| • Changed Recommended Operating Conditions | 6 |
| • Changed High-Voltage General Purpose I/O (GPIO0, GPIO1) | 8 |
| • Changed Detailed Description Overview | 19 |
| • Changed Functional Block Diagram | 20 |
| • Changed Internal Power Source Selection | 22 |
| • Changed Power Path Overview | 25 |

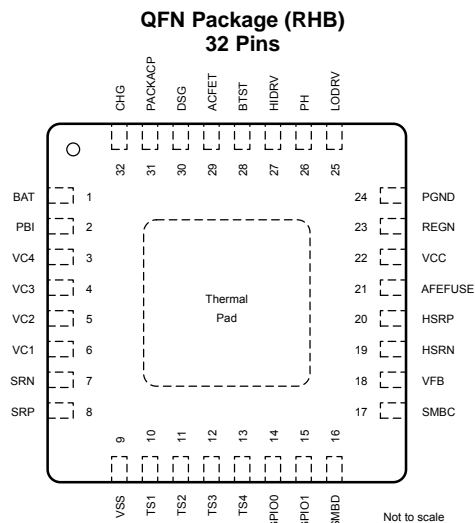
Revision History (continued)

- Changed [Typical Application Schematic](#) 30

5 Description (continued)

The device provides an array of battery and system safety functions, including overcurrent in discharge, short circuit in charge, and short circuit in discharge protection for the battery, as well as FET protection for the N-CH FETs, internal AFE watchdog, and cell disconnection detection. Through firmware, the device can provide a larger array of protection features including overvoltage, undervoltage, overtemperature, and more.

6 Pin Configuration and Functions



Pin Functions

| PIN | | | DESCRIPTION |
|-------|--------|--------------------|---|
| NAME | NUMBER | I/O ⁽¹⁾ | |
| BAT | 1 | P | Battery input pin. Primary power supply |
| PBI | 2 | P | Power supply backup input pin |
| VC4 | 3 | IA | Sense voltage input pin for the most positive cell, balance current input for the most positive cell, and battery stack measurement input |
| VC3 | 4 | IA | Sense voltage input pin for the third most positive cell, balance current input for the third most positive cell, and return balance current for the most positive cell |
| VC2 | 5 | IA | Sense voltage input pin for the second most positive cell, balance current input for the second most positive cell, and return balance current for the most positive cell |
| VC1 | 6 | IA | Sense voltage input pin for the least positive cell, balance current input for the least positive cell, and return balance current for the second most positive cell |
| SRN | 7 | IA | Analog input pin connected to the internal coulomb counter peripheral for integrating a small voltage between SRP and SRN, where SRP is the top of the sense resistor. |
| SRP | 8 | IA | Analog input pin connected to the internal coulomb counter peripheral for integrating a small voltage between SRP and SRN, where SRP is the top of the sense resistor. |
| VSS | 9 | P | Device ground |
| TS1 | 10 | IA | Thermistor input for temperature sensor channel 1 |
| TS2 | 11 | IA | Thermistor input for temperature sensor channel 2 |
| TS3 | 12 | IA | Thermistor input for temperature sensor channel 3 |
| TS4 | 13 | IA | Thermistor input for temperature sensor channel 4 |
| GPIO0 | 14 | I/O | Multi-function I/O (open drain). For more information, see <i>IO Configuration</i> in the <i>bq40z60 Technical Reference Manual</i> (SLUUA04). |

(1) P = Power Connection, O = Digital Output, IA = Analog Input, I = Digital Input, I/OD = Digital Input/Output

Pin Functions (continued)

| PIN | | | DESCRIPTION |
|---------|--------|--------------------|--|
| NAME | NUMBER | I/O ⁽¹⁾ | |
| GPIO1 | 15 | I/O | Multi-function I/O (open drain). See <i>IO Configuration</i> in the <i>bq40z60 Technical Reference Manual</i> (SLUUA04). |
| SMBD | 16 | I/OD | SMBus data pin |
| SMBCLK | 17 | I/OD | SMBus clock pin |
| VFB | 18 | IA | Feedback sense input for charger control loop |
| HSRN | 19 | IA | High sense resistor negative node input |
| HSRP | 20 | IA | High sense resistor positive node input |
| AFEFUSE | 21 | O | Fuse drive output pin |
| VCC | 22 | P | Power supply input |
| REGN | 23 | O | Charger FET gate drive regulator |
| PGND | 24 | P | Power ground |
| LODRV | 25 | O | Low side charging FET gate control output |
| PH | 26 | I/O | Charger phase signal input |
| HIDRV | 27 | O | High side charging FET gate control output |
| BTST | 28 | IA | High side bootstrap capacitor input |
| ACFET | 29 | O | AC FET gate control output |
| DSG | 30 | O | N-CH FET drive output pin |
| ACP | 31 | IA | Adapter input pin |
| CHG | 32 | O | N-CH FET drive output pin |

7 Specifications

7.1 Absolute Maximum Ratings

Over-operating free-air temperature range (unless otherwise noted)⁽¹⁾

| | | MIN | TYP | MAX | UNIT |
|------------------------------------|-------------------------------|----------------|-----|---|------|
| Supply voltage range, V_{Supply} | BAT, VCC, PBI | −0.3 | | 30 | V |
| | REGN | −0.3 | | 7 | V |
| Input voltage range, V_{IN} | ACP, SMBC, SMBD, GPIO0, GPIO1 | −0.3 | | 30 | V |
| | TS1, TS2, TS3, TS4 | −0.3 | | $V_{REG} + 0.3$ | V |
| | SRP, SRN | −0.3 | | 0.3 | V |
| | HSRP, HSRN | −0.3 | | 30 | V |
| | PH | −0.3 | | 32 | V |
| | VFB | −0.3 | | 16 | V |
| | VC4 | $VC3 - 0.3$ | | $VC3 + 8.5\text{ V, or }V_{SS} + 30$ | V |
| | VC3 | $VC2 - 0.3$ | | $VC2 + 8.5\text{ V, or }V_{SS} + 30$ | V |
| | VC2 | $VC1 - 0.3$ | | $VC1 + 8.5\text{ V, or }V_{SS} + 30$ | V |
| | VC1 | $V_{SS} - 0.3$ | | $V_{SS} + 8.5\text{ V, or }V_{SS} + 30$ | V |
| Output voltage range, V_O | CHG, DSG | −0.3 | | 32 | V |
| | HIDRV, BTST, ACFET | −0.3 | | 36 | V |
| | LODRV | −0.3 | | 7 | V |
| | AFFUSE | −0.3 | | 30 | V |
| Maximum VSS current, I_{SS} | | | 50 | | mA |
| Functional Temperature, T_{FUNC} | | −40 | | 110 | °C |

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

| | | VALUE | UNIT |
|--------------------|--------------------|-------|------|
| $V_{(ESD)}$ Rating | HBM ⁽¹⁾ | ±2000 | V |
| | CDM ⁽²⁾ | ±500 | V |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| | | MIN | NOM | MAX | UNIT |
|---------------------------------------|-------------------------------------|------|------|------|------|
| V_{Supply} Supply voltage | BAT, VCC, PBI | 2.2 | | 26 | V |
| | ACFET, BTST | 0 | | 35 | V |
| | REGN | 0 | | 6.5 | V |
| $V_{SHUTDOWN-}$ Shutdown voltage | $V_{ACP} < V_{SHUTDOWN-}$ | 1.8 | 2.0 | 2.2 | V |
| $V_{SHUTDOWN+}$ Start-up voltage | $V_{ACP} > V_{SHUTDOWN-} + V_{HYS}$ | 2.05 | 2.25 | 2.45 | V |
| V_{HYS} Shutdown voltage hysteresis | $V_{SHUTDOWN+} - V_{SHUTDOWN-}$ | | 250 | | mV |

Recommended Operating Conditions (continued)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| | | MIN | NOM | MAX | UNIT |
|-----------|------------------------|-------------------------------|-----------|---------------|------------------|
| V_{IN} | Input voltage range | ACP, SMBC, SMBD, GPIO0, GPIO1 | | 26 | V |
| | | TSx | | V_{REG} | |
| | | SRP, SRN | -0.2 | 0.2 | |
| | | HSRP, HSRN | -0.5 | 0.5 | |
| | | PH | -2 | V_{ACP} | |
| | | VFB | 0 | 14 | |
| | | VC4 | V_{VC3} | $V_{VC3} + 5$ | |
| | | VC3 | V_{VC2} | $V_{VC2} + 5$ | |
| | | VC2 | V_{VC1} | $V_{VC1} + 5$ | |
| | | VC1 | V_{VSS} | $V_{VSS} + 5$ | |
| V_O | Output voltage range | CHG, DSG, AFEFUSE | | 26 | V |
| | | HIDRV | | 35 | V |
| | | LODRV | 0 | 6.5 | V |
| C_{PBI} | External PBI capacitor | | 2.2 | | μF |
| T_{OPR} | Operating temperature | | -40 | 85 | $^\circ\text{C}$ |

7.4 Thermal Information

| THERMAL METRIC ⁽¹⁾ | | bq40z60 | UNIT |
|---------------------------------|--|------------|--------------------|
| | | RHB (VQFN) | |
| | | 32 PINS | |
| $R_{\theta JA, \text{ High K}}$ | Junction-to-ambient thermal resistance | 36 | $^\circ\text{C/W}$ |
| $R_{\theta JC(\text{top})}$ | Junction-to-case(top) thermal resistance | 31.5 | $^\circ\text{C/W}$ |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | 8 | $^\circ\text{C/W}$ |
| Ψ_{JT} | Junction-to-top characterization parameter | 0.5 | $^\circ\text{C/W}$ |
| Ψ_{JB} | Junction-to-board characterization parameter | 7.9 | $^\circ\text{C/W}$ |
| $R_{\theta JC(\text{bot})}$ | Junction-to-case(bottom) thermal resistance | 2.2 | $^\circ\text{C/W}$ |

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, [SPRA953](#).

7.5 Supply Voltage

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-------------|------------------------|---------------------------------|-----|------|------|
| V_{CC} | Device Operating Range | Operation with charger enabled | 4.0 | 25 | V |
| | | Operation with charger disabled | 2.5 | 25 | |
| V_{CC-UV} | Undervoltage lock out | VCC falling | 2.2 | 2.45 | V |

7.6 Supply Current

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---|-----|------|------|---------------|
| I_{NORMAL} NORMAL mode ⁽¹⁾ | CPU = ACTIVE, HFO = ON, ADC_FILTER = ON, CC_FILTER = ON, LFO = ON, REG18 = ON, CHG = ON, DSG = ON, ADC = ON, CC = ON, Charger Enabled, No Communication | | 1250 | 1850 | μA |
| | CPU = HALT, HFO = ON, ADC_FILTER = ON, CC_FILTER = ON, LFO = ON, REG18 = ON, CHG = ON, DSG = ON, ADC = ON, CC = ON, Charger Disabled, No Communication | | 310 | 445 | |
| I_{SLEEP} SLEEP mode ⁽¹⁾ | CPU = HALT, HFO = ON, ADC_FILTER = OFF, CC_FILTER = OFF, LFO = ON, REG18 = ON, CHG = ON, DSG = ON, ADC = OFF, CC = OFF, Charger Disabled, No Communication | | 122 | 183 | μA |
| | CPU = HALT, HFO = OFF, ADC_FILTER = OFF, CC_FILTER = OFF, LFO = ON, REG18 = ON, CHG = ON, DSG = ON, ADC = OFF, CC = OFF, Charger Disabled, No Communication | | 92 | 138 | |
| | CPU = HALT, HFO = ON, ADC_FILTER = OFF, CC_FILTER = OFF, LFO = ON, REG18 = ON, CHG = OFF, DSG = OFF, ADC = OFF, CC = OFF, Charger Disabled, No Communication | | 82 | 128 | |
| | CPU = HALT, HFO = OFF, ADC_FILTER = OFF, CC_FILTER = OFF, LFO = ON, REG18 = ON, CHG = OFF, DSG = OFF, ADC = OFF, CC = OFF, Charger Disabled, No Communication | | 52 | 83 | |
| I_{SHUTDOWN} SHUTDOWN mode | CPU = HALT, HFO = OFF, ADC_FILTER = OFF, CC_FILTER = OFF, LFO = OFF, REG18 = OFF, CHG = OFF, DSG = OFF, ADC = OFF, CC = OFF, Charger Disabled, No Communication | | 0.5 | 2 | μA |

(1) $V_{\text{CC}} \leq 20 \text{ V}$ when CHG = ON and DSG = ON

7.7 Power Supply Control

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{\text{CC}} = 10.8 \text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{\text{CC}} = 2.2 \text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--|-----|------|-----|---------------|
| $V_{\text{SWITCHOVER-}}$ BAT to VCC switchover voltage | $V_{\text{BAT}} < V_{\text{SWITCHOVER-}}$ | 2.0 | 2.1 | 2.2 | V |
| $V_{\text{SWITCHOVER+}}$ VCC to BAT switchover voltage | $V_{\text{BAT}} > V_{\text{SWITCHOVER-}} + V_{\text{HYS}}$ | 3.0 | 3.1 | 3.2 | V |
| V_{HYS} Switchover voltage hysteresis | $V_{\text{SWITCHOVER+}} - V_{\text{SWITCHOVER-}}$ | | 1000 | | mV |
| I_{LKG} Input leakage current | BAT pin, BAT = 0 V, VCC = 25 V | | | 1 | μA |
| | VCC pin, BAT = 25 V, VCC = 0 V | | | 1 | |
| | BAT and VCC pins, BAT = 0 V, VCC = 0 V, PBI = 25 V | | | 1 | |
| R_{PD} Internal pulldown resistance | ACP | 30 | 40 | 50 | k Ω |

7.8 Low-Voltage General Purpose I/O (TSx)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{\text{CC}} = 10.8 \text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{\text{CC}} = 2.2 \text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-------------------------------------|-----------------------------------|------------------------------|------------------------------|-----|------|
| V_{IH} High-level input | | $0.65 \times V_{\text{REG}}$ | | | V |
| V_{IL} Low-level input | | | $0.35 \times V_{\text{REG}}$ | | V |
| V_{OH} Output voltage high | $I_{\text{OH}} = -1.0 \text{ mA}$ | $0.75 \times V_{\text{REG}}$ | | | V |
| | $I_{\text{OH}} = -10 \mu\text{A}$ | | | | |
| V_{OL} Output voltage low | $I_{\text{OL}} = 1.0 \text{ mA}$ | | $0.2 \times V_{\text{REG}}$ | | V |

Low-Voltage General Purpose I/O (TSx) (continued)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------------------|-----------------|-----|-----|-----|---------------|
| C_{IN} Input capacitance | | | 5 | | pF |
| I_{LKG} Input leakage current | | | | 1 | μA |

7.9 High-Voltage General Purpose I/O (GPIO0, GPIO1)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------------------|--|-----|-----|------|---------------|
| V_{IH} High-level input | | 1.3 | | | V |
| V_{IL} Low-level input | | | | 0.55 | V |
| V_{OH} Output voltage high | $V_{BAT} > 5.5\text{ V}$, $I_{OH} = -0\text{ }\mu\text{A}$ | 3.5 | | | V |
| | $V_{BAT} > 5.5\text{ V}$, $I_{OH} = -10\text{ }\mu\text{A}$ | 1.8 | | | |
| V_{OL} Output voltage low | $I_{OL} = 1.5\text{ mA}$ | | | 0.4 | V |
| C_{IN} Input capacitance | | | 5 | | pF |
| I_{LKG} Input leakage current | | | | 1 | μA |
| R_O Output reverse resistance | Between GPIO0/1 and PBI | 5 | | | k Ω |

7.10 AFE Power-On Reset

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---------------------------|------|------|------|---------------|
| V_{REGIT-} Negative-going voltage input | V_{REG} | 1.51 | 1.55 | 1.59 | V |
| V_{HYS} Power-on reset hysteresis | $V_{REGIT+} - V_{REGIT-}$ | 70 | 100 | 130 | mV |
| t_{RST} Power-on reset time | | 200 | 300 | 400 | μs |

7.11 Internal 1.8-V LDO

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---|-------|--------------|------|------|
| V_{REG} Regulator voltage | | 1.6 | 1.8 | 2.0 | V |
| $\Delta V_{O(TEMP)}$ Regulator output over temperature | $\Delta V_{REG}/\Delta T_A$, $I_{REG} = 10\text{ mA}$ | | $\pm 0.25\%$ | | |
| $\Delta V_{O(LINE)}$ Line regulation | $\Delta V_{REG}/\Delta V_{BAT}$, $V_{BAT} = 10\text{ mA}$ | -0.6% | | 0.5% | |
| $\Delta V_{O(LOAD)}$ Load regulation | $\Delta V_{REG}/\Delta I_{REG}$, $I_{REG} = 0\text{ mA}$ to 10 mA | -1.5% | | 1.5% | |
| I_{REG} Regulator output current limit | $V_{REG} = 0.9 \times V_{REG(NOM)}$, $V_{IN} > 2.2\text{ V}$ | 20 | | | mA |
| I_{SC} Regulator short-circuit current limit | $V_{REG} = 0 \times V_{REG(NOM)}$ | 25 | 40 | 50 | mA |
| $PSRR_{REG}$ Power supply rejection ratio | $\Delta V_{BAT}/\Delta V_{REG}$, $I_{REG} = 10\text{ mA}$, $V_{IN} > 2.5\text{ V}$, $f = 10\text{ Hz}$ | | 40 | | dB |
| V_{SLEW} Slew rate enhancement voltage threshold | | 1.58 | 1.65 | | V |

7.12 Current Wake Comparator

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--------------------------------|-----------|-------------|-----------|------------------|
| V_{WAKE} Wake voltage threshold | $V_{WAKE} = V_{SRP} - V_{SRN}$ | ± 0.3 | ± 0.625 | ± 0.9 | mV |
| | $V_{WAKE} = V_{SRP} - V_{SRN}$ | ± 0.6 | ± 1.25 | ± 1.8 | |
| | $V_{WAKE} = V_{SRP} - V_{SRN}$ | ± 1.2 | ± 2.5 | ± 3.6 | |
| | $V_{WAKE} = V_{SRP} - V_{SRN}$ | ± 2.4 | ± 5.0 | ± 7.2 | |
| $V_{WAKE(DRIFT)}$ Temperature drift of V_{WAKE} accuracy | | | 0.5% | | $^\circ\text{C}$ |
| t_{WAKE} Time from application of current to wake | | | 0.25 | 0.5 | ms |
| $t_{WAKE(SU)}$ Wake comparator startup time | | | 500 | 1000 | μs |

7.13 Coulomb Counter⁽¹⁾

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------------|---|----------------|-------------|---------------|------------------------------|
| Input voltage range | | -0.1 | | 0.1 | V |
| Full scale range | | $-V_{REF1}/10$ | | $V_{REF1}/10$ | V |
| Integral nonlinearity ⁽²⁾ | 16-bit, Best fit over input voltage range | | ± 5.2 | ± 22.3 | LSB |
| Offset error | 16-bit, Post-calibration | | ± 5 | ± 10 | μV |
| Offset error drift | 15-bit + sign, Post-calibration | | 0.2 | 0.3 | $\mu\text{V}/^\circ\text{C}$ |
| Gain error | 15-bit + sign, Over input voltage range | | $\pm 0.2\%$ | $\pm 0.8\%$ | FSR ⁽³⁾ |
| Gain error drift | 15-bit + sign, Over input voltage range | | | 150 | PPM/ $^\circ\text{C}$ |
| Effective input resistance | | 2.5 | | | M Ω |

(1) Coulomb counter electrical specifications are assured when battery charging function is disabled.

(2) 1 LSB = $V_{REF1}/(10 \times 2^N) = 1.215/(10 \times 2^{15}) = 3.71\text{ }\mu\text{V}$

(3) Full-scale reference

7.14 CC Digital Filter

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------|-------------------|-----|-----|-----|------|
| Conversion time | Single conversion | | 250 | | ms |
| Effective resolution | Single conversion | 15 | | | Bits |

7.15 ADC⁽¹⁾

Over-operating free-air temperature range (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------------|--|-----------|----------|----------------------|---------------|
| Input voltage range | Internal reference (V_{REF1}) | -0.2 | | 1 | V |
| | External reference (V_{REG}) | -0.2 | | $0.8 \times V_{REG}$ | |
| Full scale range | $V_{FS} = V_{REF1}$ or V_{REG} | $-V_{FS}$ | | V_{FS} | V |
| Integral nonlinearity ⁽²⁾ | 16-bit, Best fit, -0.1 V to $0.8 \times V_{REF1}$ | | | ± 6.6 | LSB |
| | 16-bit, Best fit, -0.2 V to -0.1 V | | | ± 13.1 | |
| Offset error ⁽³⁾ | 16-bit, Post-calibration, $V_{FS} = V_{REF1}$ | | ± 67 | ± 157 | μV |

(1) ADC electrical specifications are assured when battery charging function is disabled.

(2) 1 LSB = $V_{REF1}/(2^N) = 1.225/(2^{15}) = 37.4\text{ }\mu\text{V}$ (when ADCTL[SPEED1, SPEED0] = 0, 0)

(3) For VC1-VSS, VC2-VC1, VC3-VC2, VC3-VSS, ACP-VSS, and $V_{REF1}/2$, the offset error is multiplied by (1/ADC multiplexer scaling factor (K)).

ADC⁽¹⁾ (continued)

Over-operating free-air temperature range (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------------|---|-----|-------------|-------------|-------------------|
| Offset error drift | 16-bit, Post-calibration, $V_{FS} = V_{REF1}$ | | 0.6 | 3 | $\mu V/^{\circ}C$ |
| Gain error | 16-bit, $-0.1 V$ to $0.8 \times V_{FS}$ | | $\pm 0.2\%$ | $\pm 0.8\%$ | FSR |
| Gain error drift | 16-bit, $-0.1 V$ to $0.8 \times V_{FS}$ | | | 150 | PPM/ $^{\circ}C$ |
| Effective input resistance | | 8 | | | M Ω |

7.16 ADC Digital Filter

Typical values stated where $T_A = 25^{\circ}C$ and $V_{CC} = 10.8 V$, Min/Max values stated where $T_A = -40^{\circ}C$ to $85^{\circ}C$ and $V_{CC} = 2.2 V$ to $26 V$ (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------|--|-----|-------|-----|------|
| Conversion time | ADCTL[SPEED1, SPEED0] = 0, 0 | | 31.25 | | ms |
| | ADCTL[SPEED1, SPEED0] = 0, 1 | | 15.63 | | |
| | ADCTL[SPEED1, SPEED0] = 1, 0 | | 7.81 | | |
| | ADCTL[SPEED1, SPEED0] = 1, 1 | | 1.95 | | |
| Resolution | No missing codes, ADCTL[SPEED1, SPEED0] = 0, 0 | 16 | | | Bits |
| Effective resolution | With sign, ADCTL[SPEED1, SPEED0] = 0, 0 | 14 | 15 | | Bits |
| | With sign, ADCTL[SPEED1, SPEED0] = 0, 1 | 13 | 14 | | |
| | With sign, ADCTL[SPEED1, SPEED0] = 1, 0 | 11 | 12 | | |
| | With sign, ADCTL[SPEED1, SPEED0] = 1, 1 | 9 | 10 | | |

7.17 ADC Multiplexer

Typical values stated where $T_A = 25^{\circ}C$ and $V_{CC} = 10.8 V$, Min/Max values stated where $T_A = -40^{\circ}C$ to $85^{\circ}C$ and $V_{CC} = 2.2 V$ to $26 V$ (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------------------|--|--------|--------|-----------------------|---------|
| K Scaling factor | VC1–VSS, VC2–VC1, VC3–VC2, VC4–VC3 | 0.1980 | 0.2000 | 0.2020 | — |
| | VC4–VSS, ACP–VSS | 0.049 | 0.050 | 0.051 | |
| | V_{REF2} | 0.490 | 0.500 | 0.510 | |
| | HSRN–VSS | 0.049 | 0.050 | 0.051 | |
| V_{IN} Input voltage range | VC4–VSS, ACP–VSS | –0.2 | | 20 | V |
| | TSx | –0.2 | | $0.8 \times V_{REF1}$ | |
| | TSx | –0.2 | | $0.8 \times V_{REG}$ | |
| I_{LKG} Input leakage current | VC1, VC2, VC3, VC4, cell balancing off, cell detach detection off, ADC multiplexer off | | | 1 | μA |

7.18 Cell Balancing Support

Typical values stated where $T_A = 25^{\circ}C$ and $V_{CC} = 10.8 V$, Min/Max values stated where $T_A = -40^{\circ}C$ to $85^{\circ}C$ and $V_{CC} = 2.2 V$ to $26 V$ (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|--|-----|-----|-----|----------|
| R_{CB} Internal cell balance resistance | $R_{DS(ON)}$ for internal FET switch at $2 V < V_{DS} < 4 V$ | | | 200 | Ω |

7.19 Cell Detach Detection

Typical values stated where $T_A = 25^{\circ}C$ and $V_{CC} = 10.8 V$, Min/Max values stated where $T_A = -40^{\circ}C$ to $85^{\circ}C$ and $V_{CC} = 2.2 V$ to $26 V$ (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---------------------|-----|-----|-----|---------|
| I_{CD} Internal cell detach check current | $VCx > VSS + 0.8 V$ | 30 | 50 | 70 | μA |

7.20 Internal Temperature Sensor

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--|-------|-------|-------|----------------------|
| V_{TEMP} Internal temperature sensor voltage drift | V_{TEMPPP} | -1.9 | -2.0 | -2.1 | mV/ $^\circ\text{C}$ |
| | $V_{TEMPPP} - V_{TEMPN}$, assured by design | 0.177 | 0.178 | 0.179 | |

7.21 NTC Thermistor Measurement Support (ADCx)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|-----------------|------|------|------|-----------------------|
| $R_{NTC(PU)}$ Internal pullup resistance | | 14.4 | 18 | 21.6 | k Ω |
| $R_{NTC(DRIFT)}$ Resistance drift over temperature | | -360 | -280 | -200 | PPM/ $^\circ\text{C}$ |

7.22 High-Frequency Oscillator

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------|--|-------|--------------|------|---------------|
| f_{HFO} Operating frequency | | | 16.78 | | MHz |
| $f_{HFO(ERR)}$ Frequency error | $T_A = -20^\circ\text{C}$ to 70°C , includes frequency drift | -2.5% | $\pm 0.25\%$ | 2.5% | |
| | $T_A = -40^\circ\text{C}$ to 85°C , includes frequency drift | -3.5% | $\pm 0.25\%$ | 3.5% | |
| $t_{HFO(SU)}$ Start-up time | $T_A = -20^\circ\text{C}$ to 85°C , CLKCTL[HFRAMP] = 1, oscillator frequency within $\pm 3\%$ of nominal | | | 4 | ms |
| | CLKCTL[HFRAMP] = 0, oscillator frequency within $\pm 3\%$ of nominal | | | 100 | μs |

7.23 Low-Frequency Oscillator

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|--|-------|--------------|------|------|
| f_{LFO} Operating frequency | | | 262.144 | | kHz |
| $f_{LFO(ERR)}$ Frequency error | $T_A = -20^\circ\text{C}$ to 70°C , includes frequency drift | -1.5% | $\pm 0.25\%$ | 1.5% | |
| | $T_A = -40^\circ\text{C}$ to 85°C , includes frequency drift | -2.5 | ± 0.25 | 2.5 | |
| $f_{LFO(FAIL)}$ Failure detection frequency | | 30 | 80 | 100 | kHz |

7.24 Voltage Reference 1

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--|------|----------|------|-----------------------|
| V_{REF1} Internal reference voltage | $T_A = 25^\circ\text{C}$, after trim | 1.21 | 1.215 | 1.22 | V |
| $V_{REF1(DRIFT)}$ Internal reference voltage drift | $T_A = 0^\circ\text{C}$ to 60°C , after trim | | ± 50 | | PPM/ $^\circ\text{C}$ |
| | $T_A = -40^\circ\text{C}$ to 85°C , after trim | | ± 80 | | |

7.25 Voltage Reference 2

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--|------|----------|------|-----------------------|
| V_{REF2} Internal reference voltage | $T_A = 25^\circ\text{C}$, after trim | 1.22 | 1.225 | 1.23 | V |
| $V_{REF2(DRIFT)}$ Internal reference voltage drift | $T_A = 0^\circ\text{C}$ to 60°C , after trim | | ± 50 | | PPM/ $^\circ\text{C}$ |
| | $T_A = -40^\circ\text{C}$ to 85°C , after trim | | ± 80 | | |

7.26 Instruction Flash

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------------|---|------|-----|-----|---------------|
| Data retention | | 10 | | | Years |
| Flash programming write cycles | | 1000 | | | Cycles |
| $t_{PROGWORD}$ Word programming time | $T_A = -40^\circ\text{C}$ to 85°C | | | 40 | μs |
| $t_{MASSERASE}$ Mass-erase time | $T_A = -40^\circ\text{C}$ to 85°C | | | 40 | ms |
| $t_{PAGEERASE}$ Page-erase time | $T_A = -40^\circ\text{C}$ to 85°C | | | 40 | ms |
| $I_{FLASHREAD}$ Flash-read current | $T_A = -40^\circ\text{C}$ to 85°C | | | 2 | mA |
| $I_{FLASHWRITE}$ Flash-write current | $T_A = -40^\circ\text{C}$ to 85°C | | | 5 | mA |
| $I_{FLASHERASE}$ Flash-erase current | $T_A = -40^\circ\text{C}$ to 85°C | | | 15 | mA |

7.27 Data Flash

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------------|---|-------|-----|-----|---------------|
| Data retention | | 10 | | | Years |
| Flash programming write cycles | | 20000 | | | Cycles |
| $t_{PROGWORD}$ Word programming time | $T_A = -40^\circ\text{C}$ to 85°C | | | 40 | μs |
| $t_{MASSERASE}$ Mass-erase time | $T_A = -40^\circ\text{C}$ to 85°C | | | 40 | ms |
| $t_{PAGEERASE}$ Page-erase time | $T_A = -40^\circ\text{C}$ to 85°C | | | 40 | ms |
| $I_{FLASHREAD}$ Flash-read current | $T_A = -40^\circ\text{C}$ to 85°C | | | 1 | mA |
| $I_{FLASHWRITE}$ Flash-write current | $T_A = -40^\circ\text{C}$ to 85°C | | | 5 | mA |
| $I_{FLASHERASE}$ Flash-erase current | $T_A = -40^\circ\text{C}$ to 85°C | | | 15 | mA |

7.28 Current Protection Thresholds

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|--|-------|-------|------|------|
| V_{OCD} OCD detection threshold voltage range | $V_{OCD} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 1 | -16.6 | | -100 | mV |
| | $V_{OCD} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 0 | -8.3 | | -50 | |
| ΔV_{OCD} OCD detection threshold voltage program step | $V_{OCD} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 1 | | -5.56 | | mV |
| | $V_{OCD} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 0 | | -2.78 | | |
| V_{SCC} SCC detection threshold voltage range | $V_{SCC} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 1 | 44.4 | | 200 | mV |
| | $V_{SCC} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 0 | 22.2 | | 100 | |

Current Protection Thresholds (continued)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-------------------|--|-------|-------|------|------|
| ΔV_{SCC} | SCC detection threshold voltage program step $V_{SCC} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 1 | | 22.2 | | mV |
| | $V_{SCC} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 0 | | 11.1 | | |
| V_{SCD1} | SCD1 detection threshold voltage range $V_{SCD1} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 1 | -44.4 | | -200 | mV |
| | $V_{SCD1} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 0 | -22.2 | | -100 | |
| ΔV_{SCD1} | SCD1 detection threshold voltage program step $V_{SCD1} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 1 | | -22.2 | | mV |
| | $V_{SCD1} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 0 | | -11.1 | | |
| V_{SCD2} | SCD2 detection threshold voltage range $V_{SCD2} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 1 | -44.4 | | -200 | mV |
| | $V_{SCD2} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 0 | -22.2 | | -100 | |
| ΔV_{SCD2} | SCD2 detection threshold voltage program step $V_{SCD2} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 1 | | -22.2 | | mV |
| | $V_{SCD2} = V_{SRP} - V_{SRN}$, PROTECTION_CONTROL[RSNS] = 0 | | -11.1 | | |
| V_{OFFSET} | OCD, SCC, and SCDx offset error Post-trim | -2.5 | | 2.5 | mV |
| V_{SCALE} | OCD, SCC, and SCDx scale error No trim | -10% | | 10% | |
| | Post-trim | -5% | | 5% | |

7.29 N-CH FET Drive (CHG, DSG)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------|---|-------|-------|-------|---------------|
| Output voltage ratio | $\text{Ratio}_{DSG} = (V_{DSG} - V_{BAT})/V_{BAT}$, $2.2\text{ V} < V_{BAT} < 4.07\text{ V}$, $10\text{ M}\Omega$ between HSRN and DSG | 2.133 | 2.333 | 2.533 | — |
| | $\text{Ratio}_{CHG} = (V_{CHG} - V_{BAT})/V_{BAT}$, $2.2\text{ V} < V_{BAT} < 4.07\text{ V}$, $10\text{ M}\Omega$ between BAT and CHG | 2.133 | 2.333 | 2.533 | |
| | $\text{Ratio}_{ACFET} = (V_{ACFET} - V_{BAT})/V_{BAT}$, $2.2\text{ V} < V_{BAT} < 4.07\text{ V}$, $10\text{ M}\Omega$ between ACP and ACFET | 2.133 | 2.333 | 2.533 | |
| $V_{(FETON)}$ | Output voltage, CHG and DSG on $V_{DSG(ON)} = V_{DSG} - V_{BAT}$, $V_{BAT} \geq 4.07\text{ V}$, $10\text{ M}\Omega$ between V_{HSRN} and DSG, $V_{BAT} = 18\text{ V}$ | 9.0 | 9.5 | 10 | V |
| | $V_{CHG(ON)} = V_{CHG} - V_{BAT}$, $V_{BAT} \geq 4.07\text{ V}$, $10\text{ M}\Omega$ between BAT and CHG, $V_{BAT} = 18\text{ V}$ | 9.0 | 9.5 | 10 | |
| | ACFET $V_{ACFET(ON)} = V_{ACFET} - V_{BAT}$, $V_{BAT} \geq 4.07\text{ V}$, $10\text{ M}\Omega$ between ACP and ACFET, $V_{BAT} = 18\text{ V}$ | 9.0 | 9.5 | 10 | |
| $V_{(FETOFF)}$ | Output voltage, CHG and DSG off $V_{DSG(OFF)} = V_{DSG} - V_{ACP}$, $10\text{ M}\Omega$ between HSRN and DSG | -0.4 | | 0.4 | V |
| | $V_{CHG(OFF)} = V_{CHG} - V_{BAT}$, $10\text{ M}\Omega$ between BAT and CHG | -0.4 | | 0.4 | |
| | ACFET $V_{ACFET(OFF)} = V_{ACFET} - V_{ACP}$, $V_{BAT} \geq 4.07\text{ V}$, $10\text{ M}\Omega$ between ACP and ACFET, $V_{BAT} = 18\text{ V}$ | -0.4 | | 0.4 | |
| t_R | Rise time V_{DSG} from 0% to 35% $V_{DSG(ON)(TYP)}$, $V_{ACP} \geq 2.2\text{ V}$, $C_L = 4.7\text{ nF}$ between DSG and V_{HSRN} , $5.1\text{ k}\Omega$ between DSG and C_L , $10\text{ M}\Omega$ between V_{HSRN} and DSG | | 200 | 500 | μs |
| | V_{CHG} from 0% to 35% $V_{CHG(ON)(TYP)}$, $V_{ACP} \geq 2.2\text{ V}$, $C_L = 4.7\text{ nF}$ between CHG and BAT, $5.1\text{ k}\Omega$ between CHG and C_L , $10\text{ M}\Omega$ between BAT and CHG | | 200 | 500 | |
| | V_{ACFET} from 0% to 35% $V_{ACFET(ON)(TYP)}$, $V_{ACP} \geq 2.2\text{ V}$, $C_L = 4.7\text{ nF}$ between ACFET and ACP, $5.1\text{ k}\Omega$ between CHG and C_L , $10\text{ M}\Omega$ between ACP and ACFET | | 200 | 500 | |

N-CH FET Drive (CHG, DSG) (continued)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------|---|-----|-----|-----|---------------|
| t_F Fall time | V_{DSG} from $V_{DSG(ON)(TYP)}$ to 1 V , $V_{ACP} \geq 2.2\text{ V}$, $C_L = 4.7\text{ nF}$ between DSG and ACP, $5.1\text{ k}\Omega$ between DSG and C_L , $10\text{ M}\Omega$ between ACP and DSG | | 40 | 300 | μs |
| | V_{CHG} from $V_{CHG(ON)(TYP)}$ to 1 V , $V_{ACP} \geq 2.2\text{ V}$, $C_L = 4.7\text{ nF}$ between CHG and BAT, $5.1\text{ k}\Omega$ between CHG and C_L , $10\text{ M}\Omega$ between BAT and CHG | | 40 | 200 | |
| | V_{ACFET} from $V_{ACFET(ON)(TYP)}$ to 1 V , $V_{ACP} \geq 2.2\text{ V}$, $C_L = 4.7\text{ nF}$ between ACFET and ACP, $5.1\text{ k}\Omega$ between CHG and C_L , $10\text{ M}\Omega$ between ACP and ACFET | | 40 | 200 | |

7.30 FUSE Drive (AFEFUSE)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|-----------------|-----|-----------|---------------|
| V_{OH} Output voltage high | $V_{BAT} \geq 8\text{ V}$, $C_L = 1\text{ nF}$, $I_{AFEFUSE} = 0\text{ }\mu\text{A}$ | 6 | 7 | 8.65 | V |
| | $V_{BAT} < 8\text{ V}$, $C_L = 1\text{ nF}$, $I_{AFEFUSE} = 0\text{ }\mu\text{A}$ | $V_{BAT} - 0.1$ | | V_{BAT} | |
| V_{IH} High-level input | | 1.5 | 2.0 | 2.5 | V |
| $I_{AFEFUSE(PU)}$ Internal pullup current | $V_{BAT} \geq 8\text{ V}$, $V_{AFEFUSE} = V_{SS}$ | | 150 | 330 | nA |
| $R_{AFEFUSE}$ Output impedance | | 2 | 2.6 | 3.2 | k Ω |
| C_{IN} Input capacitance | | | 5 | | pF |
| t_{DELAY} Fuse trip detection delay | | 128 | | 256 | μs |
| t_{RISE} Fuse output rise time | $V_{BAT} \geq 8\text{ V}$, $C_L = 1\text{ nF}$, $V_{OH} = 0\text{ V}$ to 5 V | | 5 | 20 | μs |

7.31 Battery Charger Voltage Regulation (VFB)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|------|-----|------|------------|
| V_{FB} Regulation range | Based on internal DAC reference setting | 0.61 | | 1.22 | V |
| V_{FBACC} Voltage feedback accuracy | $V_{FB} = 1.22\text{ V}$ | -2% | | 2% | |
| $V_{FB(STEPS)}$ Programmable regulation steps | | | 2.5 | | mV |
| R_{VFB} Total feedback resistor divider range | | | 500 | 700 | k Ω |

7.32 Battery Charger Current Sense (HSRP, HSRN)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--|-----|-----|-----|------|
| $V_{IN(Normal\ range)}$ Differential Input range | DAC range for current measurement | 2 | | 100 | mV |
| V_{ACC} Measurement accuracy | $V_{HSRP} - V_{HSRN} = 50\text{ mV}$, $R_{Sense} = 10\text{ m}\Omega$ | -5% | | 5% | |

7.33 Battery Charger Precharge Current Sense (HSRP, HSRN)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--|------|-----|-----|------|
| $V_{IN(\text{Normal range})}$ Differential Input range | DAC range for current measurement | 2 | | 20 | mV |
| V_{ACC} Measurement accuracy | $V_{HSRP} - V_{HSRN} = 2\text{ mV}$, $R_{Sense} = 10\text{ m}\Omega$ ($V_{HSRN} > 2.3\text{ V}$) | -70% | | 70% | |

7.34 AC Adapter Fault Detect (HSRN, VCC)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|--------------------------------------|-----|-----|-----|------|
| $V_{HSRN} - V_{CC}$ AC adapter input fault detect | Battery > AC adapter input (Falling) | 150 | 225 | 300 | mV |
| V_{Hys} Recovery hysteresis | AC adapter input > Battery (Rising) | 50 | 100 | 150 | mV |

7.35 Battery Charger Overcurrent Detection (V_{HSRP} , V_{HSRN})

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---|-----|-----|-----|------|
| $I_{OC(\text{max})}$ Charger overcurrent threshold | Charging current as a percentage of max sense voltage range | | 180 | 200 | mV |
| $I_{OC(\text{min})}$ Charger overcurrent threshold | Minimum charging overcurrent detected | 45 | 55 | | mV |

7.36 Battery Charger Undercurrent Detection (V_{HSRP} , V_{HSRN})

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--|-----|-----|-----|------|
| $I_{UC(\text{Detect})}$ Detect under current for negative inductor current | $V_{HSRP} - V_{HSRN} < 0\text{ mV}$, for negative inductor current, $V_{HSRP} > 2.3\text{ V}$ | 1 | 5 | 16 | mV |
| $I_{UC(\text{Non-synch})}$ Minimum sense voltage to enter non-synchronous mode | | | 1.7 | | mV |

7.37 System Operation Detection (V_{HSRN})

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--------------------|------|------|------|------|
| V_{HSRN} Input voltage for operation | V_{HSRN} Falling | 2.05 | 2.15 | 2.25 | V |
| V_{Hys} Recovery hysteresis | V_{HSRN} Rising | 100 | 150 | 200 | mV |

7.38 Battery Overvoltage Comparator (VFB)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|--------------------------------------|-----|------|-----|------|
| $V_{OV(\text{max})}$ Battery over-voltage detection | $V_{FB} > \text{Set value}$ (Rising) | | 106% | | |
| $V_{OV(\text{Recovery})}$ Battery over-voltage recovery | $V_{FB} < V_{OV}$ (Falling) | | 103% | | |

7.39 Regulator (REGN)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|--|-----|------|------|------|
| V_{LODRV} Gate drive for low side charger FET | $V_{CC} > 10\text{ V}$, $I_{\text{Load}} = 0$ to 60 mA | 5.7 | 6.0 | 6.3 | V |
| I_{SC} Short circuit current limit | $V_{\text{LODRV}} = 0\text{ V}$ | 60 | | | mA |
| V_{REGN} Power good indicator | V_{REGN} Rising | 3.6 | 3.68 | 3.75 | V |
| V_{Hys} Hysteresis | V_{REGN} Falling | 240 | 260 | 280 | mV |

7.40 PWM High-Side Driver (HiDRV)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|-----|-----|-----|----------|
| R_{ON} Driver turn ON resistance | $V_{\text{BTST}} - V_{\text{PH}} \geq 5.5\text{ V}$ | | 6.0 | 8.6 | Ω |
| R_{OFF} Driver turn OFF resistance | $V_{\text{FB}} < V_{\text{OV}}$ (Falling) | | 2.5 | 3.3 | Ω |
| $V_{\text{BOOTSTRAP}}$ Bootstrap refresh comparator | $V_{CC} = 4\text{ V}$ to 6 V | 2.6 | 2.9 | | V |
| | $V_{CC} > 6\text{ V}$ | 3.9 | 4.1 | | V |

7.41 PWM Low-Side Driver (LoDRV)

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|-----|-----|-----|----------|
| R_{ON} Driver turn ON resistance | $V_{\text{REGN}} - V_{\text{PGND}} \geq 5.5\text{ V}$ | 5.2 | | 7.6 | Ω |
| R_{OFF} Driver turn OFF resistance | $V_{\text{FB}} < V_{\text{OV}}$ (Falling) | 1.9 | | 2.4 | Ω |

7.42 PWM Information

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|-----------------|-----|-----|-------|------|
| t_{DEADTIME} Deadtime between FET driver output switching | | | 30 | | ns |
| Duty cycle | | | | 99.5% | |
| f_{SW} PWM switching frequency | | 0.8 | 1.0 | 1.1 | MHz |

7.43 Charger Power-Up Sequence

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|-----------------|-----|-----|-----|------|
| t_{DELAY} Power-up sequence | | | 8 | | ms |
| $t_{\text{SS(STEPS)}}$ Soft start steps | | | 8 | | |
| $t_{\text{SS(STEP TIME)}}$ Soft start time | | | 2 | | ms |

7.44 Thermal Shutdown Comparator

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------------|-----------------|-----|-----|-----|------|
| T_{SHUTDOWN} | | | 135 | 145 | C |
| T_{Hys} | | | 12 | | C |

7.45 SMBus High Voltage I/O

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------|-----------------------|-----|-----|-----|------------------|
| V_{IH} | Input voltage high | 1.3 | | | V |
| V_{IL} | Input voltage low | | | 0.8 | V |
| V_{OL} | Output low voltage | | | 0.4 | V |
| C_{IN} | Input capacitance | | 5 | | pF |
| I_{LKG} | Input leakage current | | | 1 | μA |
| R_{PD} | pulldown resistance | 0.7 | 1.0 | 1.3 | $\text{M}\Omega$ |

7.46 SMBus

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------|---|------------|------|------|---------------|
| f_{SMB} | SMBus operating frequency | 10 | | 100 | kHz |
| f_{MAS} | SMBus master clock frequency | | 51.2 | | kHz |
| t_{BUF} | Bus free time between start and stop | 4.7 | | | μs |
| $t_{HD(START)}$ | Hold time after (repeated) start | 4.0 | | | μs |
| $t_{SU(START)}$ | Repeated start setup time | 4.7 | | | μs |
| $t_{SU(STOP)}$ | Stop setup time | 4.0 | | | μs |
| $t_{HD(DATA)}$ | Data hold time | 300 | | | ns |
| $t_{SU(DATA)}$ | Data setup time | 250 | | | ns |
| $t_{TIMEOUT}$ | Error signal detect time | 25 | | 35 | ms |
| t_{LOW} | Clock low period | 4.7 | | | μs |
| t_{HIGH} | Clock high period | 4.0 | | 50 | μs |
| t_R | Clock rise time | 10% to 90% | | 1000 | ns |
| t_F | Clock fall time | 90% to 10% | | 300 | ns |
| $t_{LOW(SEXT)}$ | Cumulative clock low slave extend time | | | 25 | ms |
| $t_{LOW(MEXT)}$ | Cumulative clock low master extend time | | | 10 | ms |

7.47 SMBus XL

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 14.4\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

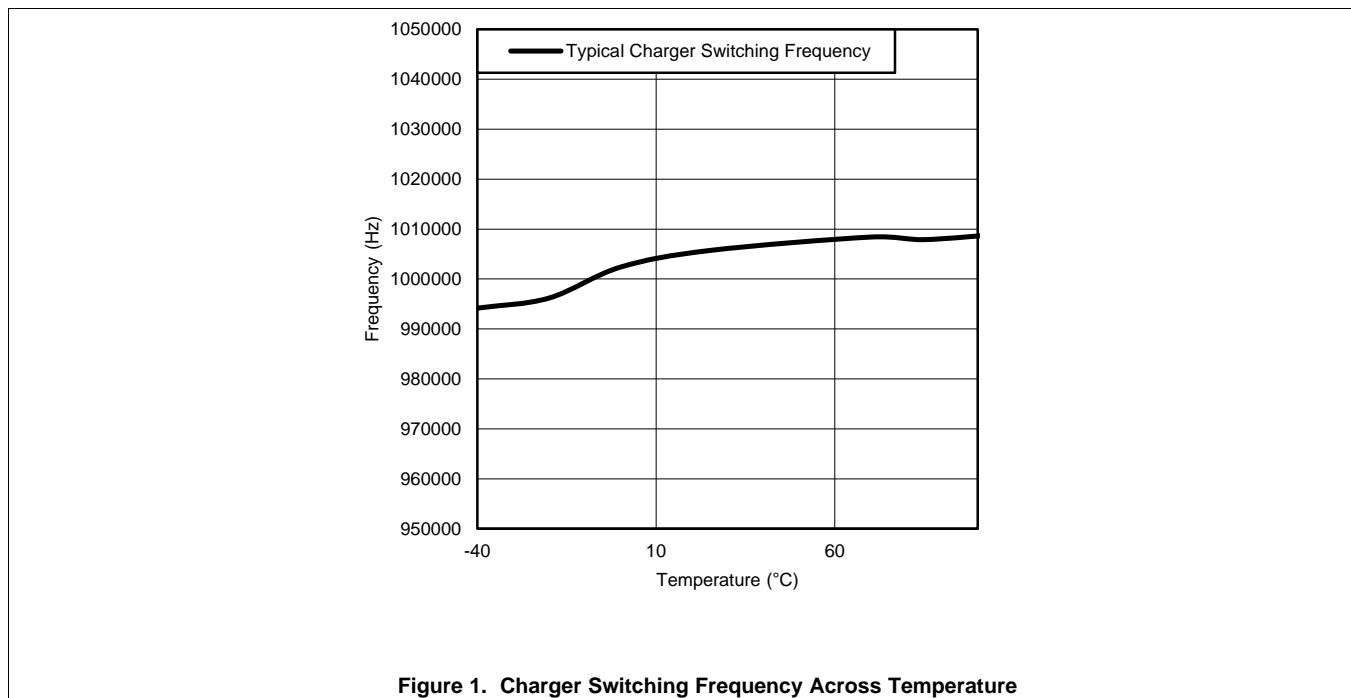
| PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------|--------------------------------------|-----|-----|-----|---------------|
| f_{SMBXL} | SMBus XL operating frequency | 40 | | 400 | kHz |
| t_{BUF} | Bus free time between start and stop | 4.7 | | | μs |
| $t_{HD(START)}$ | Hold time after (repeated) start | 4.0 | | | μs |
| $t_{SU(START)}$ | Repeated start setup time | 4.7 | | | μs |
| $t_{SU(STOP)}$ | Stop setup time | 4.0 | | | μs |
| $t_{TIMEOUT}$ | Error signal detect time | 5 | | 20 | ms |
| t_{LOW} | Clock low period | | | 20 | μs |
| t_{HIGH} | Clock high period | | | 20 | μs |

7.48 Timing Requirements

Typical values stated where $T_A = 25^\circ\text{C}$ and $V_{CC} = 10.8\text{ V}$, Min/Max values stated where $T_A = -40^\circ\text{C}$ to 85°C and $V_{CC} = 2.2\text{ V}$ to 26 V (unless otherwise noted)

| | | | MIN | TYP | MAX | UNIT |
|----------------------------------|--|--|------|------|------|---------------|
| CURRENT PROTECTION TIMING | | | | | | |
| t_{OCD} | OCD detection delay time | | 1 | | 31 | ms |
| Δt_{OCD} | OCD detection delay time program step | | | 2 | | ms |
| t_{SCC} | SCC detection delay time | | 0 | | 915 | μs |
| Δt_{SCC} | SCC detection delay time program step | | | 61 | | μs |
| t_{SCD1} | SCD1 detection delay time | PROTECTION_CONTROL[SCDDx2] = 0 | 0 | | 915 | μs |
| | | PROTECTION_CONTROL[SCDDx2] = 1 | 0 | | 1850 | |
| Δt_{SCD1} | SCD1 detection delay time program step | PROTECTION_CONTROL[SCDDx2] = 0 | | 61 | | μs |
| | | PROTECTION_CONTROL[SCDDx2] = 1 | | 121 | | |
| t_{SCD2} | SCD2 detection delay time | PROTECTION_CONTROL[SCDDx2] = 0 | 0 | | 458 | μs |
| | | PROTECTION_CONTROL[SCDDx2] = 1 | 0 | | 915 | |
| Δt_{SCD2} | SCD2 detection delay time program step | PROTECTION_CONTROL[SCDDx2] = 0 | | 30.5 | | μs |
| | | PROTECTION_CONTROL[SCDDx2] = 1 | | 61 | | |
| t_{DETECT} | Current fault detect time | $V_{\text{SRP}} - V_{\text{SRN}} = V_T - 3\text{ mV}$ for OCD, SCD1, and SC2, $V_{\text{SRP}} - V_{\text{SRN}} = V_T + 3\text{ mV}$ for SCC | | | 160 | μs |
| t_{ACC} | Current fault delay time accuracy | Max delay setting | -10% | | 10% | |

7.49 Typical Characteristics



8 Detailed Description

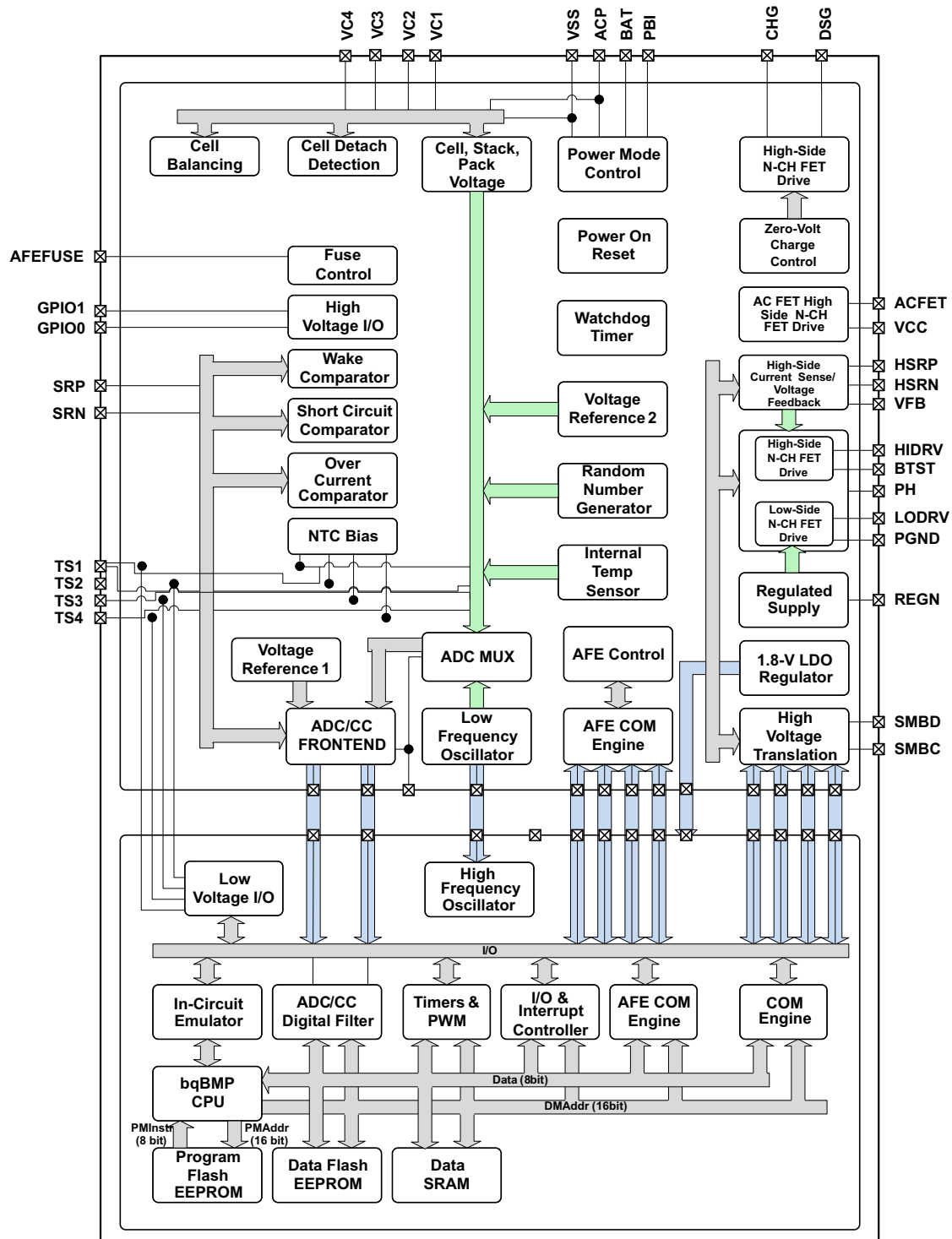
8.1 Overview

The bq40z60 is a fully integrated battery manager that employs flash-based firmware and integrated hardware protection to provide a complete solution for 2-series to 4-series cell battery stack architectures. The bq40z60 interfaces with a host system via an SBS v1.1-compliant SMBus interface, and processes instructions and data using a state-of-the-art, ultra-low-power TI bqBMP CPU. High-performance, integrated analog peripherals enable support for a sense resistor down to 5 mΩ, battery charge control, and simultaneous current/voltage data conversion for instant power calculations.

The bq40z60 controls the cell charging profile based on user-programmed data flash parameters for charging current and voltage based on temperature and cell voltage. The gas gauge provides the cell voltage and charging information to the battery charging through an internal communication bus. The charger function is controlled based on cell voltage measurements both on individual cell and total series stack readings.

The analog front end provides this voltage-based information to the charging circuit to set the profiles pre-programmed in the data flash settings, which are useful for zero voltage and PRECHARGE mode operation. The following sections detail all of the major component blocks in the bq40z60 device.

8.2 Functional Block Diagram



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8.3 Feature Description

The bq40z60 consists of an integrated analog front end, charge controller, and fuel gauge. The following sections provide an overview of the device features. For additional details, refer to the *bq40z60 Technical Reference Manual* ([SLUUA04](#)).

8.3.1 Safety Features

The bq40z60 provides support for primary safety, including:

- Cell Over/Undervoltage Protection
- Charge and Discharge Overcurrent
- Short Circuit Protection
- Charge and Discharge Overtemperature

The secondary safety features of the bq40z60 can be used to indicate more serious faults via the FUSE pin. This pin can be used to blow an in-line fuse to permanently disable the battery pack from charging or discharging. The secondary safety features provide protection against:

- Safety Over/Undervoltage Permanent Failure
- Safety Overtemperature Permanent Failure
- Safety FET Overtemperature Permanent Failure
- Qmax Imbalance Permanent Failure
- Impedance Imbalance Permanent Failure
- Capacity Degradation Permanent Failure
- Cell Balancing Permanent Failure
- Fuse Failure Permanent Failure
- Voltage Imbalance at Rest Permanent Failure
- Voltage Imbalance Active Permanent Failure
- Charge/Discharge FET Permanent Failure
- Second Level Protector Permanent Failure
- Instruction Flash Checksum Permanent Failure
- Open Cell Connection Permanent Failure
- Data Flash Permanent Failure
- Open Thermistor Permanent Failure

8.3.2 Analog Front End (AFE) Details

The analog front end (AFE) consists of circuits responsible for managing internal power and interfacing to outside components for measuring current, voltage, and temperature. The bq40z60 AFE includes an active-high interrupt output connected internally to the fuel gauge to notify it of important changes in some of the AFE registers.

The bq40z60 manages its supply voltage dynamically according to operating conditions. When $V_{BAT} > V_{SWITCHOVER-} + V_{HYS}$, the AFE connects an internal switch to BAT and uses this pin to supply power to its internal 1.8-V LDO, which subsequently powers all device logic and flash operations. Once BAT decreases to $V_{BAT} < V_{SWITCHOVER-}$, the AFE disconnects its internal switch from BAT and connects another switch to VCC, allowing sourcing of power from a charger (if present). An external capacitor connected to PBI provides a momentary supply voltage to help guard against system brownouts due to transient short-circuit or overload events that pull VBAT below $V_{SWITCHOVER-}$.

Feature Description (continued)

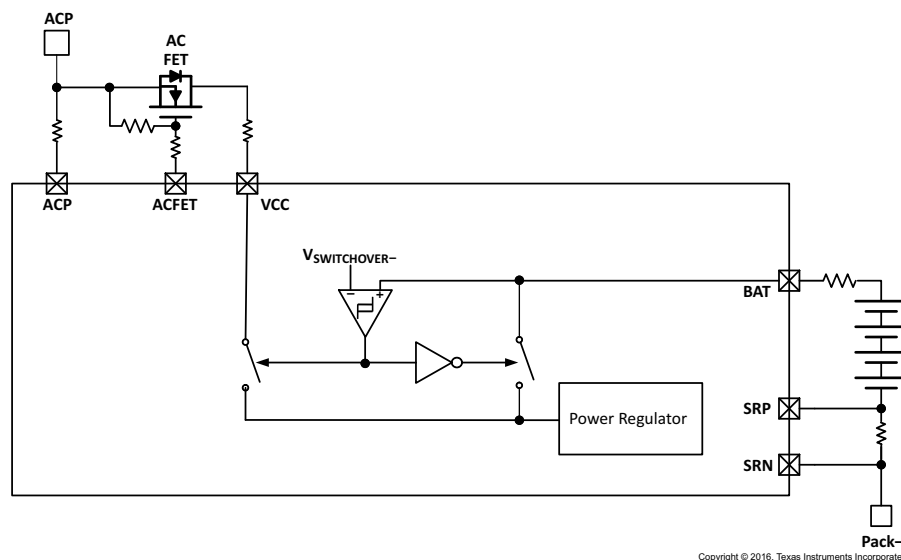


Figure 2. Internal Power Source Selection

In the event of a power-cycle, the bq40z60 AFE will hold its internal RESET output pin high for t_{RST} duration to allow its internal 1.8-V LDO and LFO to stabilize before running the analog gas gauge (AGG). The AFE enters power-on reset when the voltage at V_{REG} falls below V_{REGIT-} and exits reset when V_{REG} rises above $V_{REGIT-} + V_{HYS}$ for t_{RST} time. After t_{RST} , the bq40z60 AGG writes its trim values to the AFE.

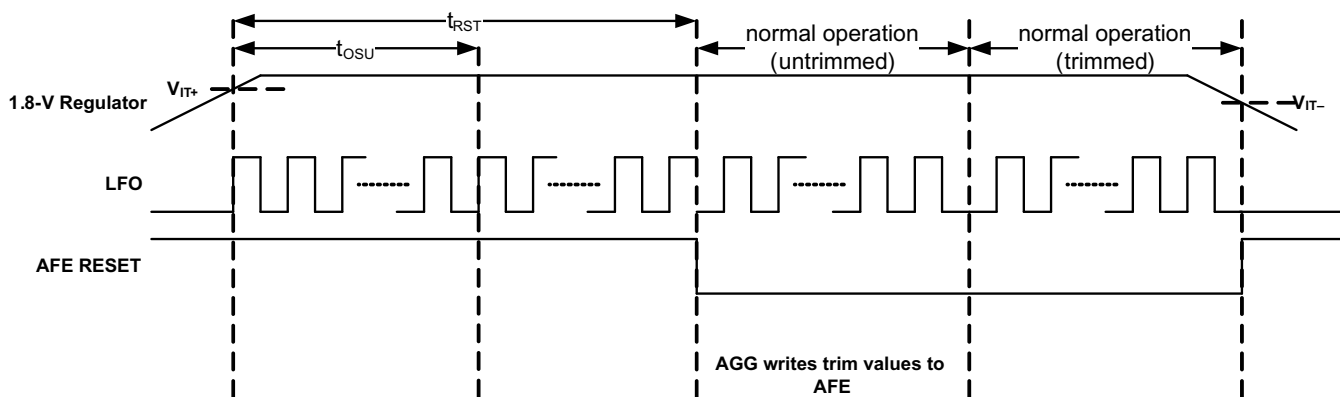


Figure 3. Power-On Reset Operation

The bq40z60 AFE includes a low frequency oscillator (LFO) running at 262.144 kHz. The AFE monitors the LFO frequency and indicates a failure via LATCH_STATUS[LFO] if the output frequency is much lower than normal.

The bq40z60 AFE provides two internal voltage references: V_{REF1} , used by the ADC and CC, and V_{REF2} used by the LDO, LFO, current wake comparator, and over- and short-current protection circuitry.

8.3.2.1 Wake Up Comparator

The internal wake comparator can be used to wake the bq40z60 from a HALT state if a configurable threshold is detected across SRP and SRN.

Feature Description (continued)

8.3.2.2 Cell Balancing Support

The integrated cell balancing FETs included in the bq40z60 device allow the AFE to bypass cell current around a given cell or numerous cells to effectively balance the entire battery stack. External series resistors placed between the cell connections and the VCx input pins set the balancing current magnitude. The cell balancing circuitry can be enabled or disabled via the CELL_BAL_DET[CB3, CB2, CB1] control register. Series input resistors between 100 Ω and 1 k Ω are recommended for effective cell balancing.

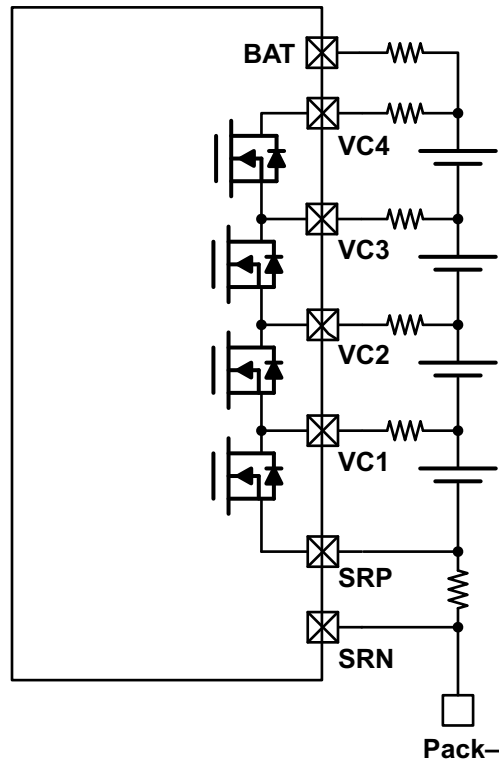


Figure 4. Cell Balancing Configuration

8.3.2.3 FET Drive

The bq40z60 controls two external N-CH MOSFETs in a back-to-back configuration for battery protection. The charge (CHG) and discharge (DSG) FETs are automatically disabled if a safety fault is detected and can also be manually turned off using AFE_CONTROL[CHGEN, DSGEN] = 0, 0. When the gate drive is disabled, an internal circuit discharges CHG to BAT and DSG to HSRN.

The AC FET (N-CH MOSFET) controls power input from the AC adaptor to the battery charging system by monitoring the voltage at the VCC pin, and turning ON the ACFET if the voltage exceeds the V_{HSRN} voltage. The following register command sets the AC FET gate drive output control, AFE_STATUS register (0x01) ACFET (Pin 2): Setting this pin to 1 allows the AC FET gate drive to be on if other conditions are satisfied.

8.3.2.4 Fuse Drive

The bq40z60 AFE has the ability to blow an external fuse in the event of a permanent failure. The fuse drive itself is supplied from the BAT input pin and its state can be monitored using the AFE_STATUS[FUSE_RAW] register. If AFE_STATUS[FUSE_RAW] = 1 for t_{DELAY} duration, then LATCH_STATUS[FUSE] is set to 1, and after an additional 500 ms, the CHG and DSG FET drive outputs will be disabled if LATCH_STATUS[FUSE] has not been cleared by then. If the AFEFUSE output is not used, it should be connected to VSS. When AFEFUSE is in the low state, it uses an internal weak pullup to enable detection of disconnection between the AFEFUSE pin and the fuse drive circuitry.

Feature Description (continued)

8.3.3 Charge Controller Details

The charge controller, under control from the fuel gauge's processor, provides autonomous control over the charging of the battery pack. The controller uses a 1-MHz buck architecture using external FETs driven by internal gate drivers. The charge voltage and current can be adjusted via data flash values to account for the temperature and voltage of the battery cells, allowing for a JEITA type charge profile. The voltage and current may also be directly written to the charge controller from an external host, allowing for a user-defined charging profile. The charger runs in Narrow Voltage DC, that is, the output voltage of the charger will only exceed the battery voltage by a small amount; by contrast, a charger that does not run in Narrow Voltage DC mode will output the adapter voltage to the system.

The charger is designed to enable the system to continue to run while the battery is charged. If the system requires more current than the charger is able to provide, the battery supplements the current to the system. The charger can support an external precharge FET, allowing the VSYS to remain above a minimum voltage needed for the system to operate.

The charger supports precharge, constant current/constant voltage, and termination, as shown below. The voltage and current thresholds for precharge and termination are controlled by data flash values. Refer to the *bq40z60 Technical Reference Manual* ([SLUUA04](#)) for more information.

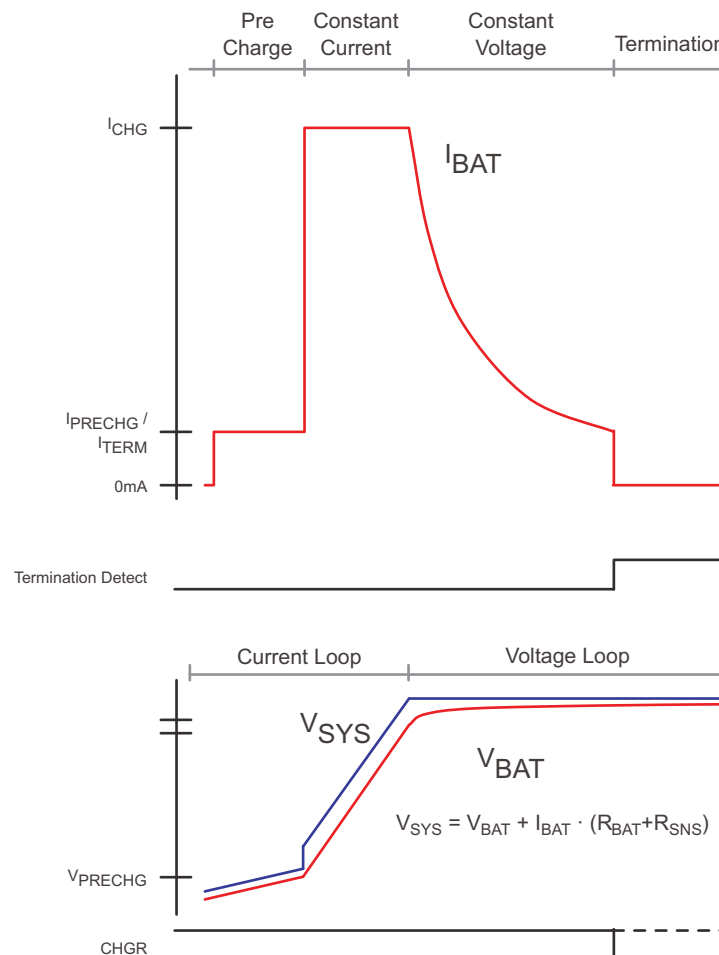


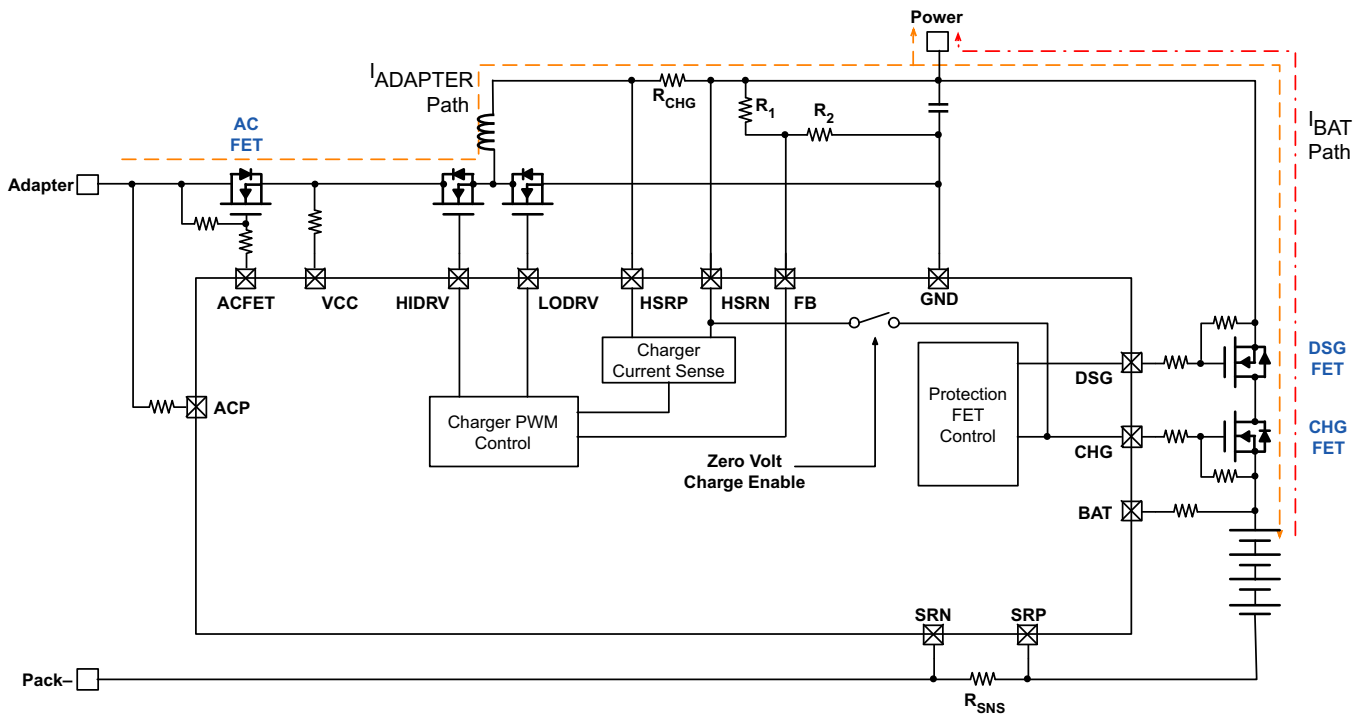
Figure 5. Normal Charge Profile

Feature Description (continued)

The charger maintains a cycle-by-cycle current limit by sensing across a resistor in series with the inductor (shown in Figure 6 as R_{CHG}). In precharge and constant voltage, the DC current is regulated by sensing the current across the sense resistor at the bottom on of the cell stack. When the charger is enabled, the initial current is set for either the Precharge or Constant Current/Constant Voltage (CC/CV) value, based on the minimum cell voltage. Once the charger enters CONSTANT CURRENT mode, the temperature and maximum cell voltage-adjusted-charging current is set, and the voltage output of the charger is automatically regulated to maintain the current across R_{CHG} . Once the temperature-adjusted voltage is reached by the charger output, the current starts to taper.

Throughout the charge cycle, the current available from the charger is limited by the *ChargingCurrent()* value. The system draws more current, however, with the battery supplementing the difference. Once battery charging is terminated, the charger is capable of supplying all of the current defined by the **Advanced Charge Algorithm: Maximum Current** Register value. Refer to the *bq40z60 Technical Reference Manual (SLUUA04)* for more information.

Figure 6 shows the system power path with the adaptor current and battery current overlaid. Further information is available in *Application and Implementation*.



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Figure 6. Power Path Overview

8.3.3.1 Precharge Modes

The charge controller is designed to allow for both internal precharge control and external precharge control. The device can operate in precharge with external FETs and a current limiting resistor. Refer to the *bq40z60 Technical Reference Manual (SLUUA04)* for more information.

8.3.3.2 Zero-Volt Charge Support

This mode of operation is similar to PRECHARGE mode switched charging, but with the charge FET operation in the saturation region. The NVDC out is connected to the CHG gate drive output internally to allow for precharge current from the charger through the CHG FET. This current is limited based on the value of the external R_{sense} (10-mΩ resistor the lowest precharge current = 200 mA). This will increase the power dissipation of the charge FET and will require thermal heat management and protection to ensure correct operation.

Feature Description (continued)

8.3.3.3 Charge Termination

Once the highest cell voltage reaches the value specified in the data flash, the charger output voltage will no longer increase and the current will start to taper. Once the highest cell voltage is within the **Charge Term Voltage** window and the measured current is below **Charge Term Taper Current** for 40 s or more, the charger will terminate by disabling the CHG FET and setting the appropriate flags. Refer to the *bq40z60 Technical Reference Manual (SLUUA04)* for more information.

The system can still provide load current from the battery pack if the adaptor current cannot support the system load. The diode of the CHG FET starts to conduct as the system voltage decreases to a point where the pack voltage is greater than the system regulation voltage – V_{diode} . If the average discharge current is high, the system can turn ON the CHG FET for improved efficiency and minimized line losses during the discharge phase.

8.3.4 Fuel Gauge and Control Details

The bq40z60 uses the Impedance Track™ algorithm to measure and calculate the available capacity in battery cells. The bq40z60 accumulates a measure of charge and discharge currents and compensates the charge current measurement for the temperature and state-of-charge of the battery. The bq40z60 estimates self-discharge of the battery and also adjusts the self-discharge estimation based on temperature. The device also has TURBO BOOST mode support, which enables the bq40z60 to provide the necessary data for the MCU to determine what level of peak power consumption can be applied without causing a system reset or a transient battery voltage level spike to trigger termination flags. See the *bq40z60 Technical Reference Manual (SLUUA04)* for further details.

8.3.4.1 Battery Trip Point (BTP)

Required for WIN8 OS, the Battery Trip Point (BTP) feature indicates when the RSOC of a battery pack has depleted to a certain value set in a DF register. This feature allows a host to program two capacity-based thresholds that govern triggering a BTP interrupt on the BTP_INT pin, and setting or clearing the *OperationStatus[BTP_INT]* on the basis of *RemainingCapacity()*.

An internal weak pullup is applied when the BTP feature is active. Depending on the system design, an external pullup may be required to put on the BTP_INT pin. See [High-Voltage General Purpose I/O \(GPIO0, GPIO1\)](#) for details.

8.3.4.2 Lifetime Data Logging Features

The bq40z60 offers lifetime data logging for several critical battery parameters. The following parameters are updated every 10 hours if a difference is detected between values in RAM and data flash:

- Maximum and Minimum Cell Voltages
- Maximum Delta Cell Voltage
- Maximum Charge Current
- Maximum Discharge Current
- Maximum Average Discharge Current
- Maximum Average Discharge Power
- Maximum and Minimum Cell Temperature
- Maximum Delta Cell Temperature
- Maximum and Minimum Internal Sensor Temperature
- Maximum FET Temperature
- Number of Safety Events Occurrences and the Last Cycle of the Occurrence
- Number of Valid Charge Termination and the Last Cycle of the Valid Charge Termination
- Number of Qmax and Ra Updates and the Last Cycle of the Qmax and Ra Updates
- Number of Shutdown Events
- Cell Balancing Time for Each Cell
(This data is updated every 2 hours if a difference is detected.)
- Total FW Runtime and Time Spent in Each Temperature Range
(This data is updated every 2 hours if a difference is detected.)

Feature Description (continued)

8.3.5 Authentication

The bq40z60 supports authentication by the host using SHA-1. More information about the algorithm can be found in the *bq40z60 Technical Reference Manual* (SLUUA04).

8.3.6 LED Display

The bq40z60 can drive a 4-segment LED display for remaining capacity indication and/or a permanent fail (PF) error code indication.

8.3.7 Internal Temperature Sensor

An internal temperature sensor is available on the bq40z60 to reduce the cost, power, and size of the external components necessary to measure temperature. It is available for connection to the ADC using the multiplexer, and is ideal for determining pack temperature during storage and IC temperature during normal operation.

8.3.8 External Temperature Sensor Support

Each of the TSx input pins can be enabled with an 18-k Ω (Typ.) linearization pullup resistor to support using a 10 k Ω (25°C) NTC external thermistor, such as the Semitec 103AT–2. One or more thermistors can be connected between VSS and the individual RCx pin. The analog measurement is then taken via the ADC through its input multiplexer. If a different thermistor type is required, then changes to the external support components may be required.

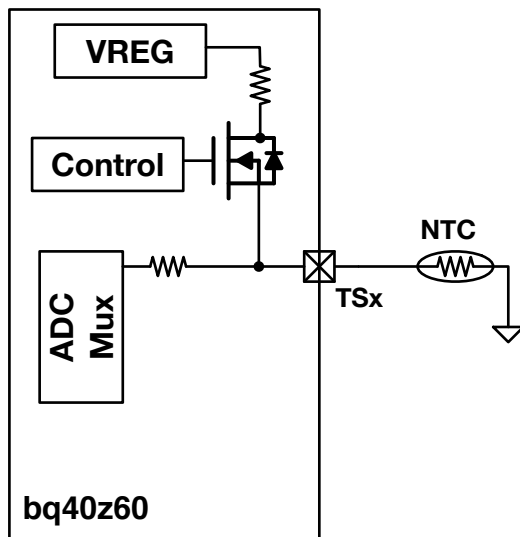


Figure 7. Thermistor Pin Configuration

8.3.9 High Frequency Oscillator

The bq40z60 includes a high frequency oscillator (HFO) running at 16.78 MHz. It is synthesized from the LFO output and scaled down to 8.388 MHz with 50% duty cycle. There is no need for external oscillator components.

8.3.10 Communications

The bq40z60 uses SMBus v1.1 with MASTER mode and packet error checking (PEC) options per the SBS specification.

Feature Description (continued)

8.3.10.1 SMBus On and Off State

The bq40z60 detects an SMBus off state when SMBC and SMBD are low for two or more seconds. Clearing this state requires that either SMBC or SMBD transition high. The communication bus will resume activity within 1 ms.

8.3.10.2 SBS Commands

The *ManufacturerAccess()* Command List shows the supported Manufacturer Access and SBS commands. See the *bq40z60 Technical Reference Manual* ([SLUUA04](#)) for further details.

Table 1. ManufacturerAccess() Command List

| FUNCTION | MANUFACTURER ACCESS COMMAND | SBS COMMAND | ACCESS | FORMAT | DATA READ ON 0x44 OR 0x23 | AVAILABLE IN SEALED MODE |
|----------------------------|-----------------------------|-------------|--------|--------|---------------------------|--------------------------|
| DeviceType | 0x0001 | | R | Block | Yes | Yes |
| FirmwareVersion | 0x0002 | | R | Block | Yes | Yes |
| HardwareVersion | 0x0003 | | R | Block | Yes | Yes |
| IFChecksum | 0x0004 | | R | Block | Yes | Yes |
| StaticDFSSignature | 0x0005 | | R | Block | Yes | Yes |
| ChemID | 0x0006 | | R | Block | Yes | Yes |
| StaticChemDFSSignature | 0x0008 | | R | Block | Yes | Yes |
| AlIDFSSignature | 0x0009 | | R | Block | Yes | Yes |
| ShutdownMode | 0x0010 | | W | — | — | Yes |
| SleepMode | 0x0011 | | W | — | — | — |
| AutoCCOfset | 0x0013 | | W | — | — | — |
| FuseToggle | 0x001D | | W | — | — | — |
| PrechargeFET | 0x001E | | W | — | — | — |
| ChargeFET | 0x001F | | W | — | — | — |
| DischargeFET | 0x0020 | | W | — | — | — |
| Gauging | 0x0021 | | W | — | — | — |
| FETControl | 0x0022 | | W | — | — | — |
| LifetimeDataCollection | 0x0023 | | W | — | — | — |
| PermanentFailure | 0x0024 | | W | — | — | — |
| BlackBoxRecorder | 0x0025 | | W | — | — | — |
| Fuse | 0x0026 | | W | — | — | — |
| LifetimeDataReset | 0x0028 | | W | — | — | — |
| PermanentFailureData Reset | 0x0029 | | W | — | — | — |
| LifetimeDataFlush | 0x002E | | W | — | — | — |
| LifetimeDataSpeedUp Mode | 0x002F | | W | — | — | — |
| BlackBoxRecorderReset | 0x002A | | W | — | — | — |
| CalibrationMode | 0x002D | | W | — | — | — |
| SealDevice | 0x0030 | | W | — | — | — |
| SecurityKeys | 0x0035 | | R/W | Block | Yes | — |
| AuthenticationKey | 0x0037 | | R/W | Block | — | — |
| DeviceReset | 0x0041 | | W | — | — | — |
| SafetyAlert | 0x0050 | 0x50 | R | Block | Yes | Yes |
| SafetyStatus | 0x0051 | 0x51 | R | Block | Yes | Yes |
| PFAAlert | 0x0052 | 0x52 | R | Block | Yes | Yes |
| PFStatus | 0x0053 | 0x53 | R | Block | Yes | Yes |
| OperationStatus | 0x0054 | 0x54 | R | Block | Yes | Yes |
| ChargingStatus | 0x0055 | 0x55 | R | Block | Yes | Yes |
| GaugingStatus | 0x0056 | 0x56 | R | Block | Yes | Yes |

Feature Description (continued)

Table 1. ManufacturerAccess() Command List (continued)

| FUNCTION | MANUFACTURER ACCESS COMMAND | SBS COMMAND | ACCESS | FORMAT | DATA READ ON 0x44 OR 0x23 | AVAILABLE IN SEALED MODE |
|--------------------------------------|-----------------------------|-------------|--------|--------|---------------------------|--------------------------|
| ManufacturingStatus | 0x0057 | 0x57 | R | Block | Yes | Yes |
| AFERegister | 0x0058 | 0x58 | R | Block | Yes | Yes |
| LifetimeDataBlock1 | 0x0060 | 0x60 | R | Block | Yes | Yes |
| LifetimeDataBlock2 | 0x0061 | 0x61 | R | Block | Yes | Yes |
| LifetimeDataBlock3 | 0x0062 | 0x62 | R | Block | Yes | Yes |
| ManufacturerInfo | 0x0070 | 0x70 | R | Block | Yes | Yes |
| DAStatus1 | 0x0071 | 0x71 | R | Block | Yes | Yes |
| DAStatus2 | 0x0072 | 0x72 | R | Block | Yes | Yes |
| GaugeStatus1 | 0x0073 | 0x73 | R | Block | Yes | Yes |
| GaugeStatus2 | 0x0074 | 0x74 | R | Block | Yes | Yes |
| GaugeStatus3 | 0x0075 | 0x75 | R | Block | Yes | Yes |
| StateofHealth | 0x0077 | | R | Block | Yes | Yes |
| CHGR_EN | 0x00C0 | | W | — | — | No |
| CVRD_ARM | 0x00C1 | | W | — | — | Yes |
| ACFETEST | 0x00C2 | | W | — | — | No |
| CHGONTEST | 0x00C3 | | W | — | — | No |
| ROMMode | 0x0F00 | | W | — | — | — |
| ExitCalibrationOutput | 0xF080 | | R/W | Block | Yes | — |
| OutputCCandADCfor Calibration | 0xF081 | | R/W | Block | Yes | — |
| OutputShortedCCand ADCforCalibration | 0xF082 | | R/W | Block | Yes | — |

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The bq40z60 is a monolithic charger and gas gauge solution for multi-cell battery packs. By integrating these devices, software control can be handed off from the host microcontroller to the gas gauge controller, providing for potential energy savings that correlate to runtime.

9.2 Typical Applications

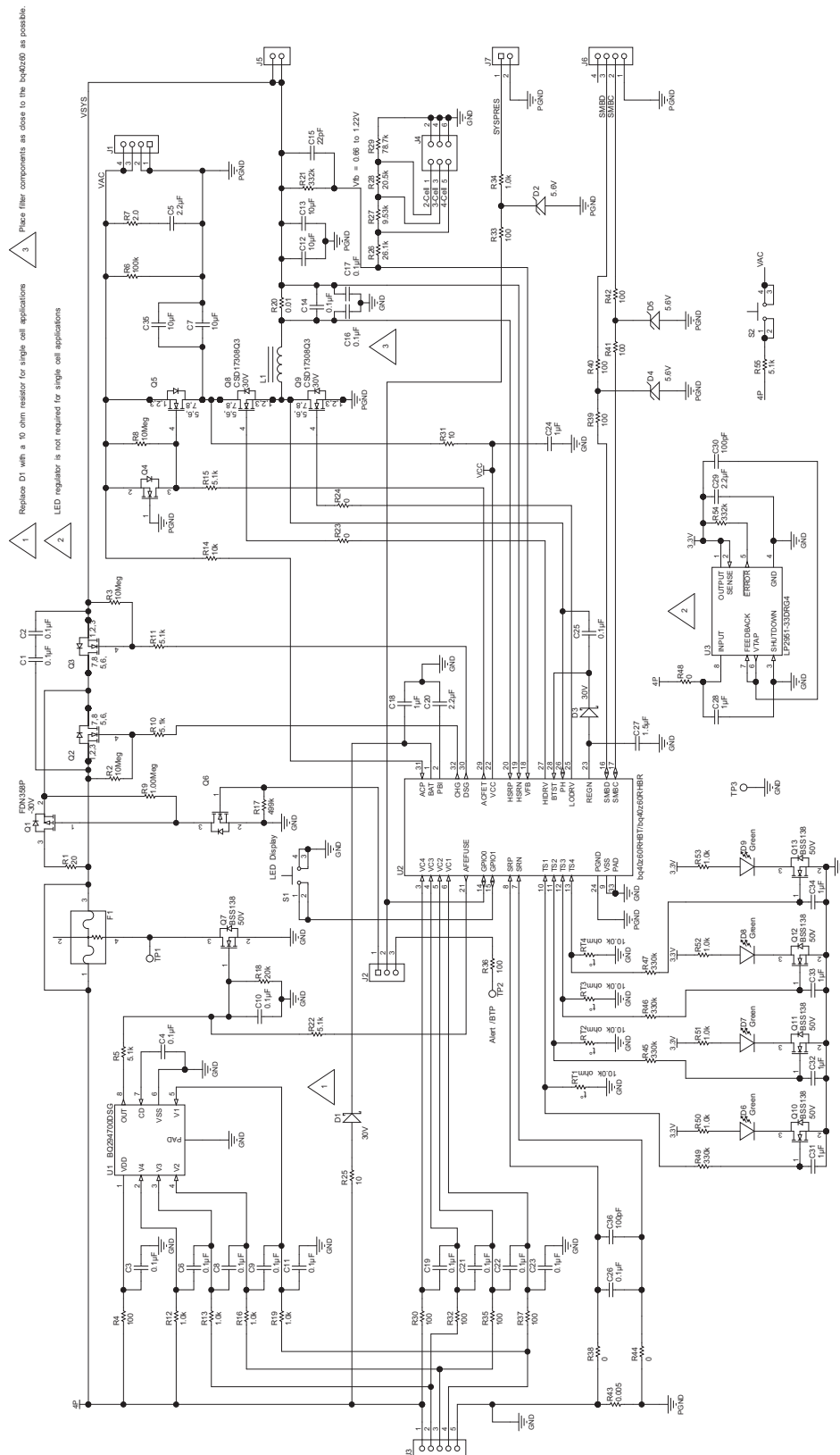


Figure 8. Typical Application Schematic

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Typical Applications (continued)

NOTE

The feedback resistor to VFB from charging output will have different values based on the number of series cells configured for charging the pack.

9.2.1 Design Requirements

For this design example, use the parameters listed in [Table 2](#) as the input parameters.

Table 2. Design Parameters

| Design Parameter | Example Value |
|------------------------------|---------------|
| Input Voltage Range | 15–22 V |
| 3-Cell Battery Voltage Range | 9 V–12.6 V |
| 4-Cell Battery Voltage Range | 12 V–16.8 V |
| Operating Frequency | 1000 kHz |

9.2.2 Detailed Design Procedure

9.2.2.1 Inductor Selection

The bq40z60 has a 1000-kHz switching frequency to allow the use of small inductor and capacitor values. Inductor saturation current should be higher than the charging current (I_{CHG}) plus half the ripple current (I_{RIPPLE}):

$$I_{SAT} \geq I_{CHG} + (1/2) I_{RIPPLE} \quad (1)$$

The inductor ripple current depends on input voltage (V_{IN}), duty cycle ($D = V_{OUT}/V_{IN}$), switching frequency (f_s) and inductance (L):

$$I_{RIPPLE} = \frac{V_{IN} \times D \times (1 - D)}{f_s \times L} \quad (2)$$

The maximum inductor ripple current happens with $D = 0.5$ or close to 0.5. For example, the battery charging voltage range is from 9 V to 12.6 V for a 3-cell battery pack. For 20-V adaptor voltage, 10-V battery voltage gives the maximum inductor ripple current. Another example is a 4-cell battery: The battery voltage range is from 12 V to 16.8 V, and 12-V battery voltage gives the maximum inductor ripple current.

Usually inductor ripple is designed in the range of (20%–40%) maximum charging current as a trade-off between inductor size and efficiency for a practical design.

The bq40z60 has cycle-by-cycle charge undercurrent protection (UCP) by monitoring the charging-current sensing resistor to prevent negative inductor current. The typical UCP threshold is 5-mV falling edge corresponding to 0.5-A falling edge for a 10-mΩ charging-current sensing resistor.

9.2.2.2 Input Capacitor

The input capacitor should have enough ripple-current rating to absorb input switching ripple current. The worst-case RMS ripple current is half of the charging current when the duty cycle is 0.5. If the converter does not operate at 50% duty cycle, then the worst-case capacitor RMS current I_{CIN} occurs where the duty cycle is closest to 50% and can be estimated using the following equation:

$$I_{CIN} = I_{CHG} \times \sqrt{D \times (1-D)} \quad (3)$$

A low-ESR ceramic capacitor such as X7R or X5R is preferred for the input-decoupling capacitor and should be placed to the drain of the high-side MOSFET and source of the low-side MOSFET as close as possible. The voltage rating of the capacitor must be higher than the normal input voltage level. A 25-V or higher-rating capacitor is preferred for 20-V input voltage. 10-μF to 20-μF capacitance is suggested for typical of 3-A to 4-A charging current.

9.2.2.3 Output Capacitor

Output capacitor also should have enough ripple-current rating to absorb the output switching ripple current. The output capacitor RMS current I_{COUT} is given:

$$I_{\text{COUT}} = \frac{I_{\text{RIPPLE}}}{2 \times \sqrt{3}} \approx 0.29 \times I_{\text{RIPPLE}} \quad (4)$$

The output capacitor voltage ripple can be calculated as follows:

$$\Delta V_o = \frac{1}{8LCf_s^2} \left(V_{\text{BAT}} - \frac{V_{\text{BAT}}^2}{V_{\text{IN}}} \right) \quad (5)$$

At a certain input/output voltage and switching frequency, the voltage ripple can be reduced by increasing the output filter LC. The bq40z60 has an internal loop compensator. To get good loop stability, the resonant frequency of the output inductor and output capacitor should be designed between 21 kHz and 27 kHz. The preferred ceramic capacitor has a 25-V or higher rating, X7R or X5R for a 4-cell application.

9.2.2.4 Power MOSFETs Selection

Two external N-CH MOSFETs are used for a synchronous switching battery charger. The gate drivers are internally integrated into the IC with 6 V of gate drive voltage. 30-V or higher voltage rating MOSFETs are preferred for 20-V input voltage, and 40 V or higher-rating MOSFETs are preferred for 20-V to 28-V input voltage.

Figure-of-merit (FOM) is usually used for selecting the proper MOSFET based on a tradeoff between the conduction loss and switching loss. For a top-side MOSFET, FOM is defined as the product of the MOSFET on-resistance, $r_{\text{DS(on)}}$, and the gate-to-drain charge, Q_{GD} . For a bottom-side MOSFET, FOM is defined as the product of the MOSFET on-resistance, $r_{\text{DS(on)}}$, and the total gate charge, Q_{G} .

$$\text{FOM}_{\text{top}} = R_{\text{DS(on)}} \times Q_{\text{GD}} \quad \text{FOM}_{\text{bottom}} = R_{\text{DS(on)}} \times Q_{\text{G}} \quad (6)$$

The lower the FOM value, the lower the total power loss. Usually a lower $r_{\text{DS(on)}}$ has a higher cost with the same package size.

The top-side MOSFET loss includes conduction loss and switching loss. It is a function of duty cycle ($D = V_{\text{OUT}}/V_{\text{IN}}$), charging current (I_{CHG}), the MOSFET on-resistance ($r_{\text{DS(on)}}$), input voltage (V_{IN}), switching frequency (f_s), turn-on time (t_{on}), and turn-off time (t_{off}):

$$P_{\text{top}} = D \times I_{\text{CHG}}^2 \times R_{\text{DS(on)}} + \frac{1}{2} \times V_{\text{IN}} \times I_{\text{CHG}} \times (t_{\text{on}} + t_{\text{off}}) \times f_s \quad (7)$$

The first item represents the conduction loss. Usually MOSFET $r_{\text{DS(on)}}$ increases by 50% with 100°C junction temperature rise. The second term represents the switching loss. The MOSFET turn-on and turn-off times are given by:

$$t_{\text{on}} = \frac{Q_{\text{SW}}}{I_{\text{on}}}, t_{\text{off}} = \frac{Q_{\text{SW}}}{I_{\text{off}}} \quad (8)$$

where Q_{SW} is the switching charge, I_{on} is the turn-on gate-driving current, and I_{off} is the turn-off gate driving current. If the switching charge is not given in the MOSFET data sheet, it can be estimated by gate-to-drain charge (Q_{GD}) and gate-to-source charge (Q_{GS}):

$$Q_{\text{SW}} = Q_{\text{GD}} + \frac{1}{2} \times Q_{\text{GS}} \quad (9)$$

Total gate-driving current can be estimated by the REGN voltage (V_{REGN}), MOSFET plateau voltage (V_{plt}), total turn-on gate resistance (R_{on}), and turn-off gate resistance (R_{off}) of the gate driver:

$$I_{\text{on}} = \frac{V_{\text{REGN}} - V_{\text{plt}}}{R_{\text{on}}}, I_{\text{off}} = \frac{V_{\text{plt}}}{R_{\text{off}}} \quad (10)$$

The conduction loss of the bottom-side MOSFET is calculated with the following equation when it operates in synchronous continuous-conduction mode:

$$P_{\text{bottom}} = (1 - D) \times I_{\text{CHG}}^2 \times R_{\text{DS(on)}} \quad (11)$$

If the HSRP–HSRN voltage decreases below 5 mV (the charger is also forced into non-synchronous mode when the average HSRP–HSRN voltage is lower than 1.7 mV), the low-side FET is turned off for the remainder of the switching cycle to prevent negative inductor current. As a result, all the freewheeling current goes through the body diode of the bottom-side MOSFET. The maximum charging current in non-synchronous mode can be up to 1.6 A (0.5 A typ) for a 10-mΩ charging-current sensing resistor, considering IC tolerance. Choose the bottom-side MOSFET with either an internal Schottky or body diode capable of carrying the maximum non-synchronous mode charging current.

MOSFET gate-driver power loss contributes to the dominant losses on the controller IC when the buck converter is switching. The combined high side and low side MOSFET gate charge, Q_{g_total} , is proportional to the power dissipation of the IC, as shown in Equation 12:

$$P_{ICLoss_driver} = V_{IN} \cdot Q_{g_total} \cdot f_s \quad (12)$$

Choosing FETs with a lower Q_{g_total} will reduce power loss.

9.2.2.5 Input Filter Design

During adaptor hot plug-in, the parasitic inductance and input capacitor from the adaptor cable form a second-order system. The voltage spike at the VCC pin may be beyond the IC maximum voltage rating and damage the IC. The input filter must be carefully designed and tested to prevent an overvoltage event on the VCC pin.

There are several methods for damping or limiting the overvoltage spike during adaptor hot plug-in. An electrolytic capacitor with high ESR as an input capacitor can damp the overvoltage spike well below the IC maximum pin voltage rating. A high-current-capability TVS Zener diode can also limit the overvoltage level to an IC safe level. However, these two solutions may not have low cost or small size.

Figure 9 shows a cost-effective and small size solution. The R1 and C1 are composed of a damping RC network to damp the hot plug-in oscillation. As a result, the overvoltage spike is limited to a safe level. D1 is used for reverse voltage protection for the VCC pin (it can be the body diode of input ACFET). C2 is a VCC pin-decoupling capacitor and it should be placed as close as possible to the VCC pin. R2 and C2 form a damping RC network to further protect the IC from high dv/dt and high-voltage spike. The C2 value should be less than the C1 value so R1 can be dominant over the ESR of C1 to get enough of a damping effect for hot plug-in. The R1 and R2 packages must be sized to handle inrush-current power loss according to the resistor manufacturer's datasheet. The filter component values always must be verified with the real application, and minor adjustments may be needed to fit in the real application circuit.

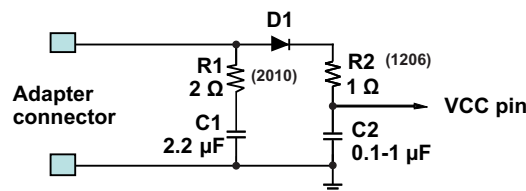
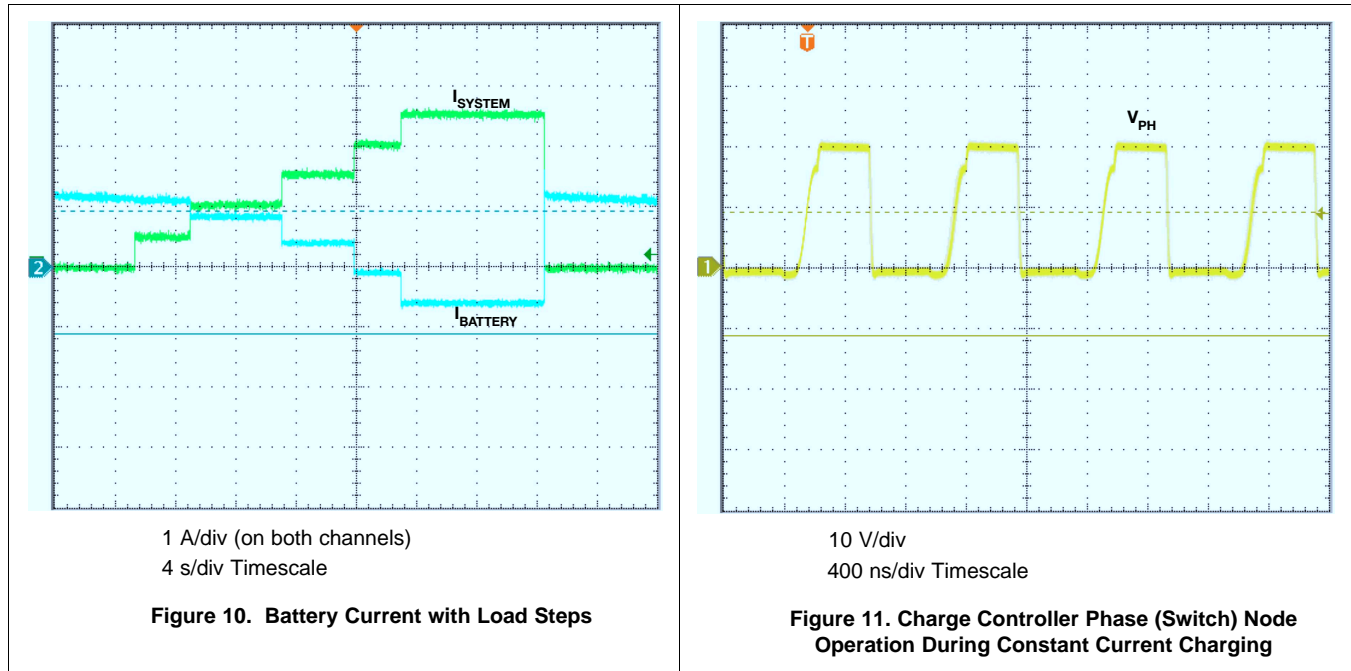


Figure 9. Input Filter

9.2.3 Application Curves



10 Power Supply Recommendations

The bq40z60 is designed to operate from a well-regulated input voltage supply range between 4.0 V and 25 V; however, with a multi-cell pack, the input voltage should be a minimum of 1 V above the maximum stack voltage. If the input supply is more than a few inches from the bq40z60, additional bulk capacitance in the form of a 47- μ F electrolytic capacitor should be used.

11 Layout

11.1 Layout Guidelines

The following information is related to external component selection and guidelines for PCB layout.

11.1.1 PCB Layout

The switching node rise and fall times should be minimized for minimum switching loss. Proper layout of the components to minimize high-frequency current-path loop (see [Figure 12](#)) is important to prevent electrical and magnetic field radiation and high-frequency resonant problems. The following is a PCB layout priority list for proper layout. Layout of the PCB according to this specific order is essential.

1. Place the input capacitor as close as possible to the switching MOSFET supply and ground connections and use the shortest possible copper trace connection. The capacitors should be placed on the same layer as the FETs instead of using vias to connect the capacitor and the FETs. Additionally, any vias connecting the input capacitor to the adaptor node should not be placed between the capacitor and the FETs; the capacitor should have a solid copper path to the FET.
2. The IC should be placed close to the switching MOSFET gate pins to keep the gate-drive signal traces short for a clean MOSFET drive. The IC can be placed on the other side of the PCB from the switching MOSFETs.
3. Place the inductor input pin as close as possible to the switching MOSFET output pin. Minimize the copper area of this trace to lower electrical and magnetic field radiation, but make the trace wide enough to carry the charging current. Do not use multiple layers in parallel for this connection. Minimize parasitic capacitance from this area to any other trace or plane.
4. The charging-current sensing resistor should be placed right next to the inductor output. Route the sense

Layout Guidelines (continued)

leads connected across the sensing resistor back to the IC in same layer, close to each other (minimize loop area) and do not route the sense leads through a high-current path (see [Figure 13](#) for Kelvin connection for best current accuracy). Place the decoupling capacitor on these traces next to the IC.

5. Place the output capacitor next to the sensing resistor output and ground.
6. Output capacitor ground connections must be tied to the same copper that connects to the input capacitor ground before connecting to system ground.
7. Place the sense resistor and filter components, R1, C2, and C3, as close as possible to the IC and directly adjacent to the decoupling capacitor between HSRN and HSRP.
8. Route the analog ground separately from the power ground and use a single ground connection to tie the charger power ground to the charger analog ground. Just beneath the IC, use the copper-pour for analog ground, but avoid power pins to reduce inductive and capacitive noise coupling. Connect analog ground to GND. Connect analog ground and power ground together using the thermal pad as the single ground connection point. Or use a 0-Ω resistor to tie analog ground to power ground (thermal pad should tie to analog ground in this case). A star connection under the thermal pad is highly recommended.
9. It is critical that the exposed thermal pad on the back side of the IC package be soldered to the PCB ground. Ensure that there are sufficient thermal vias directly under the IC connecting to the ground plane on the other layers.
10. Place decoupling capacitors next to the IC pins and make the trace connection as short as possible.
11. Size and number of all vias should be enough for a given current path.

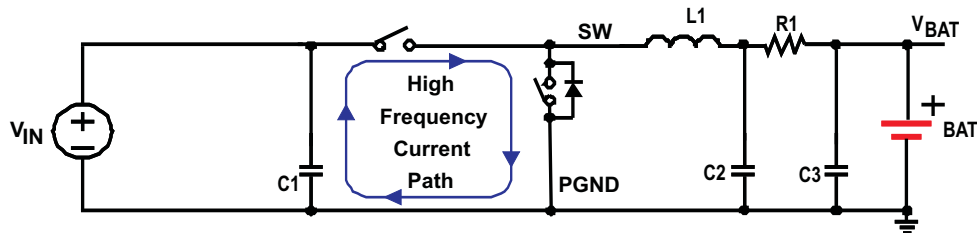


Figure 12. High-Frequency Current Path

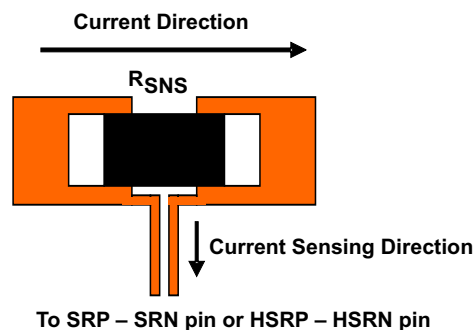


Figure 13. Sensing Resistor PCB Layout

For the recommended component placement with trace and via locations, see the *bq40z60EVM SBS 1.1 Impedance Track™ Technology Enabled Battery Management Solution Evaluation Module User's Guide* ([SLUUB71](#)).

For the QFN information, see the *Quad Flatpack No-Lead Logic Packages Application Note* ([SCBA017](#)) and the *QFN/SON PCB Attachment Application Note* ([SLUA271](#)).

11.2 Layout Example

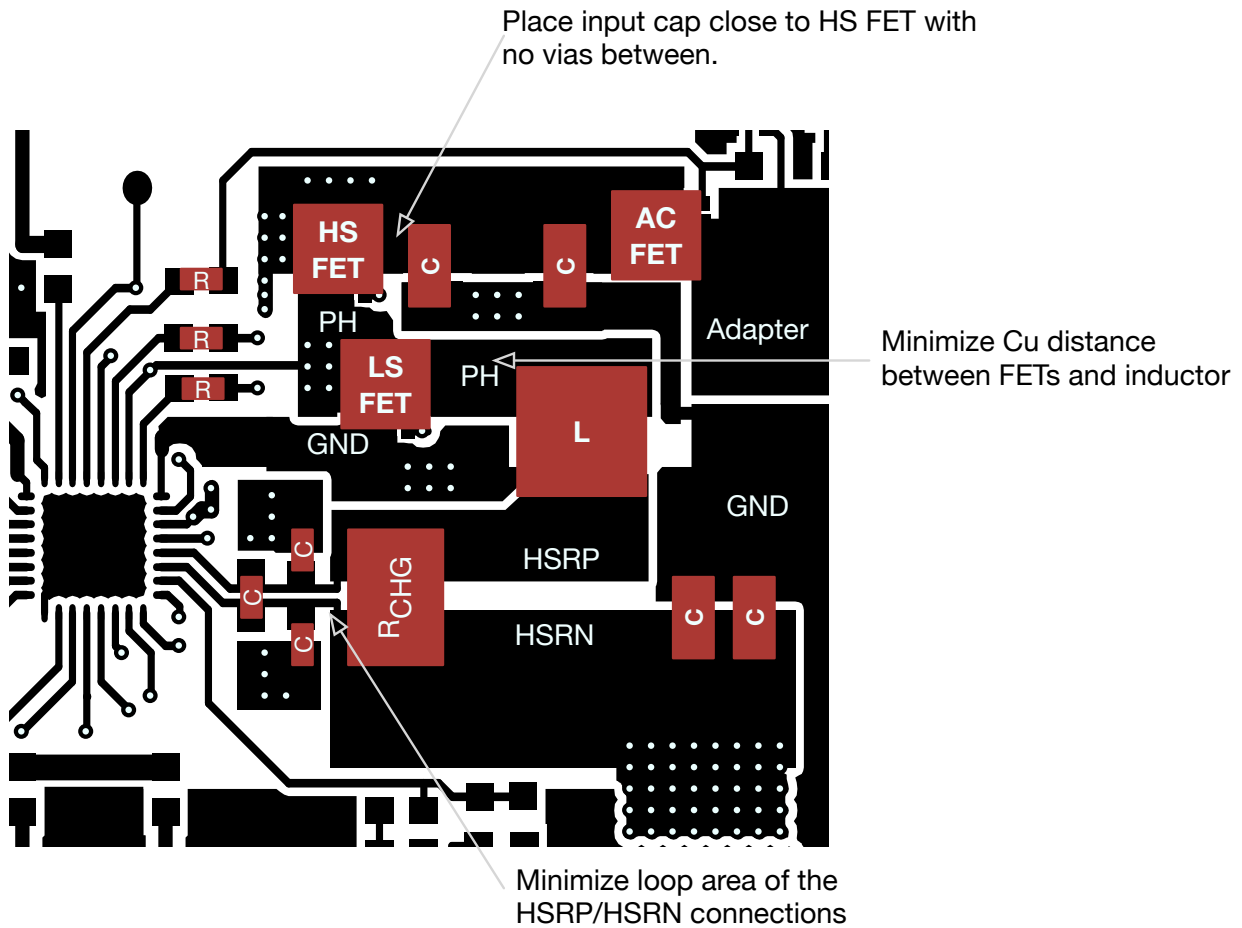


Figure 14. Board Layout Example

12 Device and Documentation Support

12.1 Related Documentation

For related documentation, see the *bq40z60 Technical Reference Manual* ([SLUUA04](#)).

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

Impedance Track, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

| Orderable part number | Status (1) | Material type (2) | Package Pins | Package qty Carrier | RoHS (3) | Lead finish/ Ball material (4) | MSL rating/ Peak reflow (5) | Op temp (°C) | Part marking (6) |
|-----------------------------|---------------|----------------------|-----------------|-----------------------|-------------|--------------------------------------|-----------------------------------|--------------|---------------------|
| BQ40Z60RHBR | Active | Production | VQFN (RHB) 32 | 3000 LARGE T&R | Yes | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BQ40Z60 |
| BQ40Z60RHBR.A | Active | Production | VQFN (RHB) 32 | 3000 LARGE T&R | Yes | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BQ40Z60 |
| BQ40Z60RHBRG4 | Active | Production | VQFN (RHB) 32 | 3000 LARGE T&R | Yes | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BQ40Z60 |
| BQ40Z60RHBRG4.A | Active | Production | VQFN (RHB) 32 | 3000 LARGE T&R | Yes | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BQ40Z60 |
| BQ40Z60RHBT | Active | Production | VQFN (RHB) 32 | 250 SMALL T&R | Yes | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BQ40Z60 |
| BQ40Z60RHBT.A | Active | Production | VQFN (RHB) 32 | 250 SMALL T&R | Yes | NIPDAU | Level-1-260C-UNLIM | -40 to 85 | BQ40Z60 |

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TAPE AND REEL INFORMATION



*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|---------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| BQ40Z60RHBR | VQFN | RHB | 32 | 3000 | 330.0 | 12.4 | 5.3 | 5.3 | 1.1 | 8.0 | 12.0 | Q2 |
| BQ40Z60RHBRG4 | VQFN | RHB | 32 | 3000 | 330.0 | 12.4 | 5.3 | 5.3 | 1.1 | 8.0 | 12.0 | Q2 |
| BQ40Z60RHBT | VQFN | RHB | 32 | 250 | 180.0 | 12.4 | 5.3 | 5.3 | 1.1 | 8.0 | 12.0 | Q2 |

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|---------------|--------------|-----------------|------|------|-------------|------------|-------------|
| BQ40Z60RHBR | VQFN | RHB | 32 | 3000 | 346.0 | 346.0 | 33.0 |
| BQ40Z60RHBRG4 | VQFN | RHB | 32 | 3000 | 346.0 | 346.0 | 33.0 |
| BQ40Z60RHBT | VQFN | RHB | 32 | 250 | 182.0 | 182.0 | 20.0 |

GENERIC PACKAGE VIEW

RHB 32

VQFN - 1 mm max height

5 x 5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4224745/A

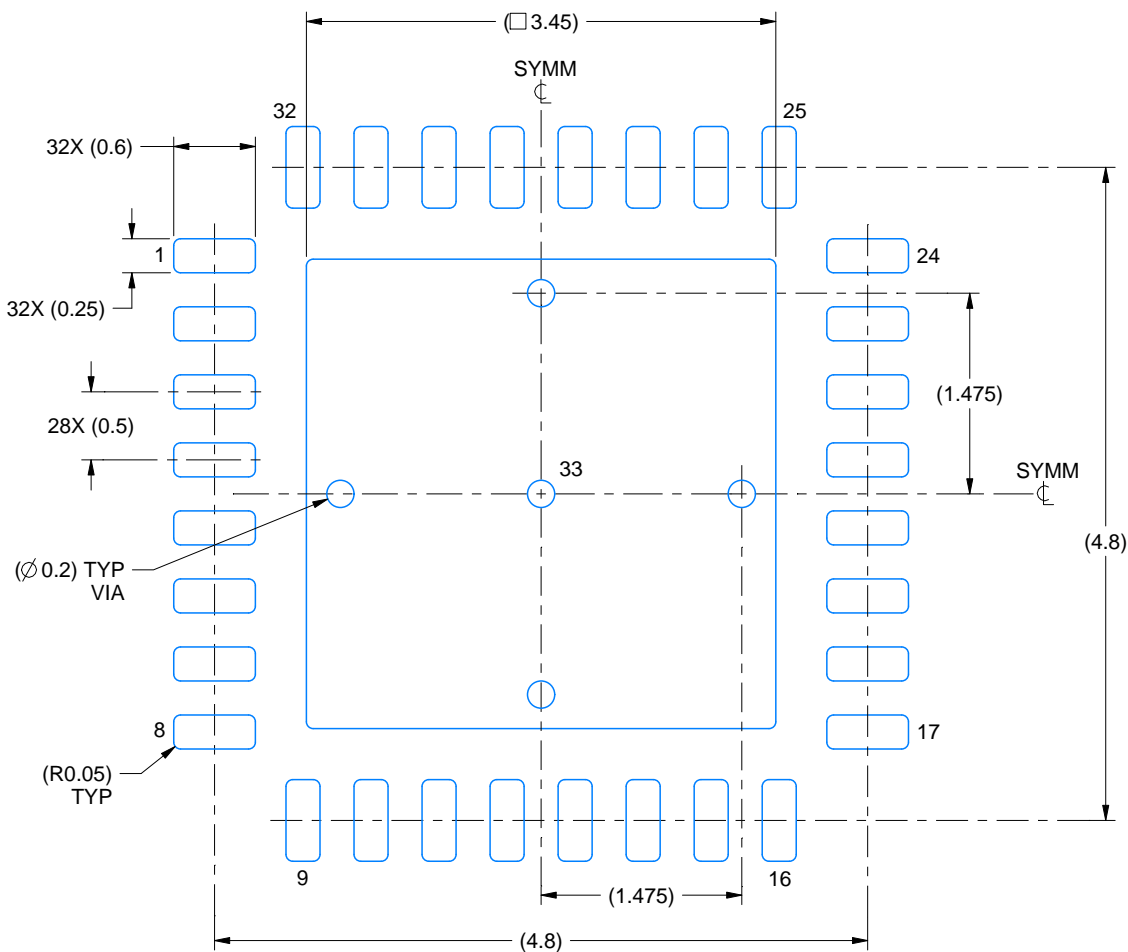
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

RHB0032E

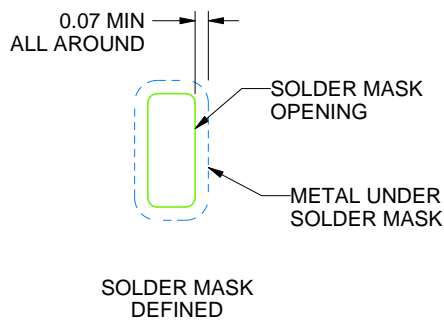
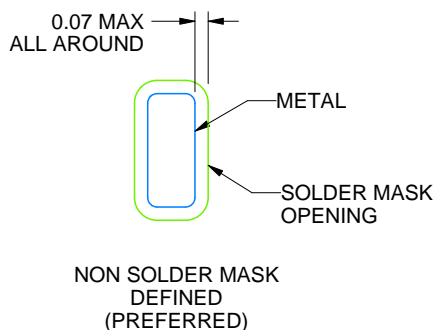
VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE

SCALE:18X



SOLDER MASK DETAILS

4223442/B 08/2019

NOTES: (continued)

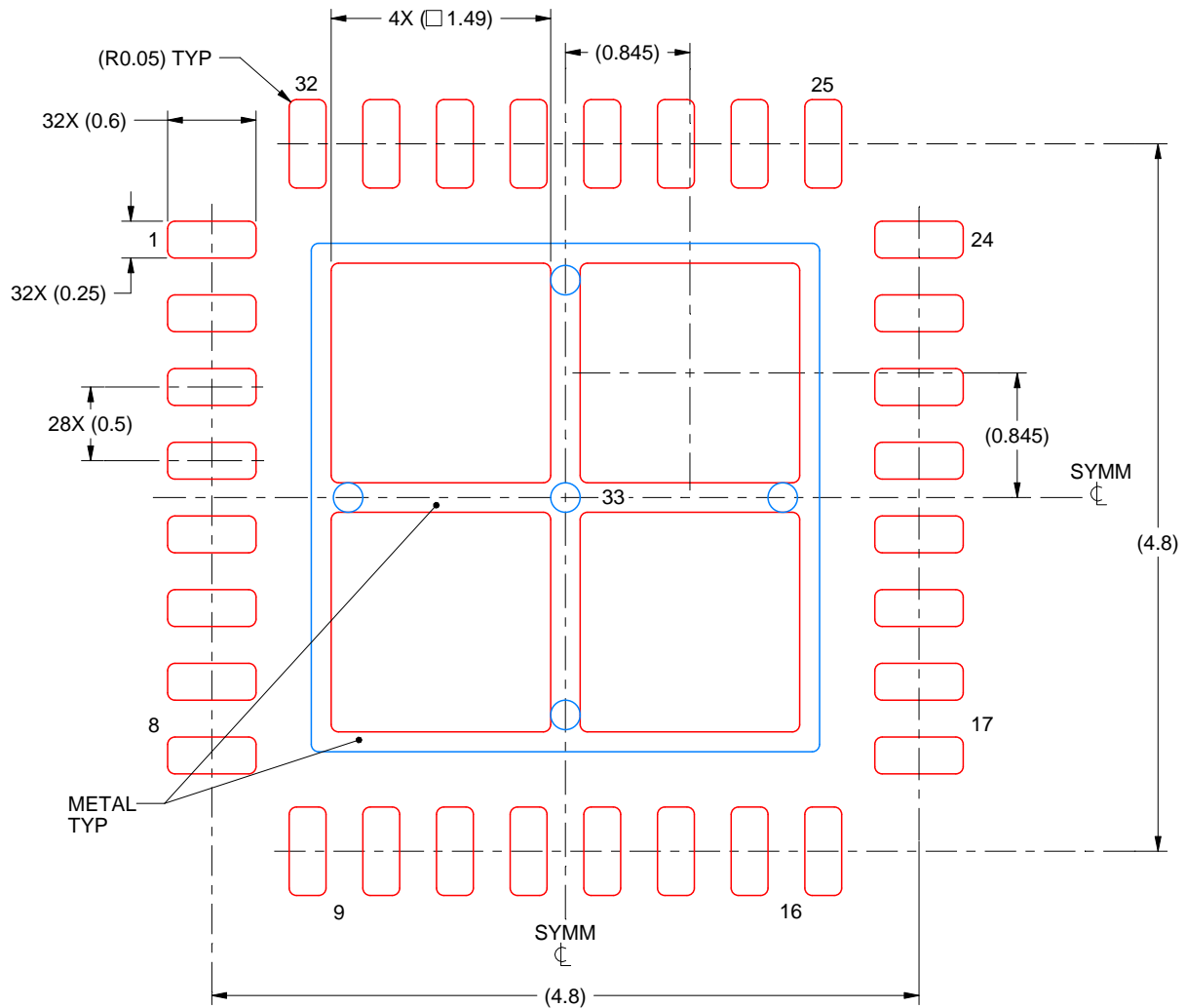
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

RHB0032E

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 33:
75% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:20X

4223442/B 08/2019

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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